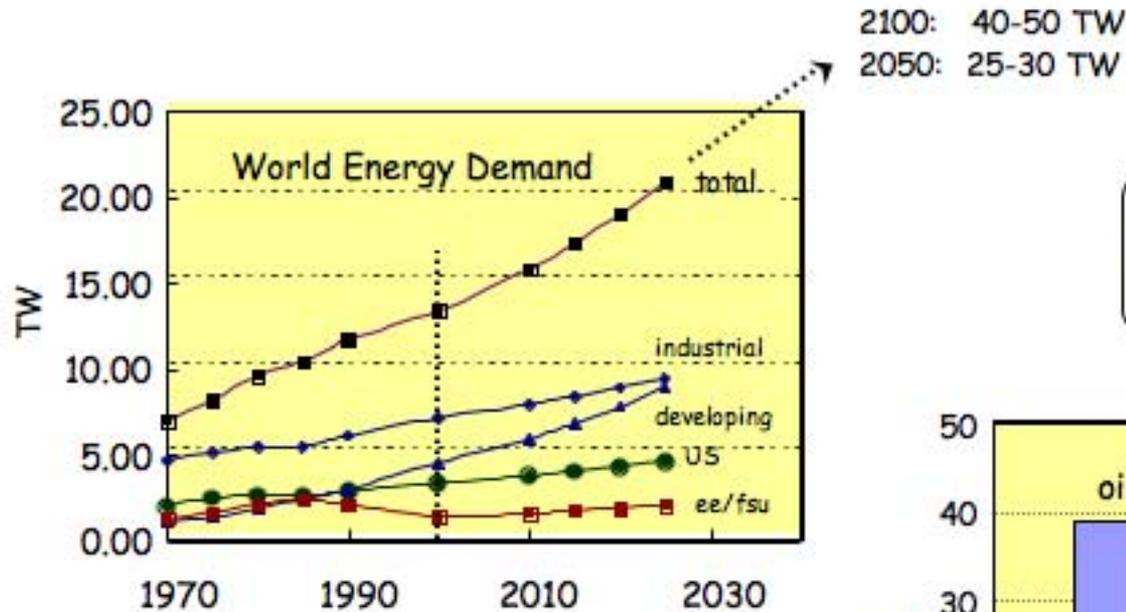
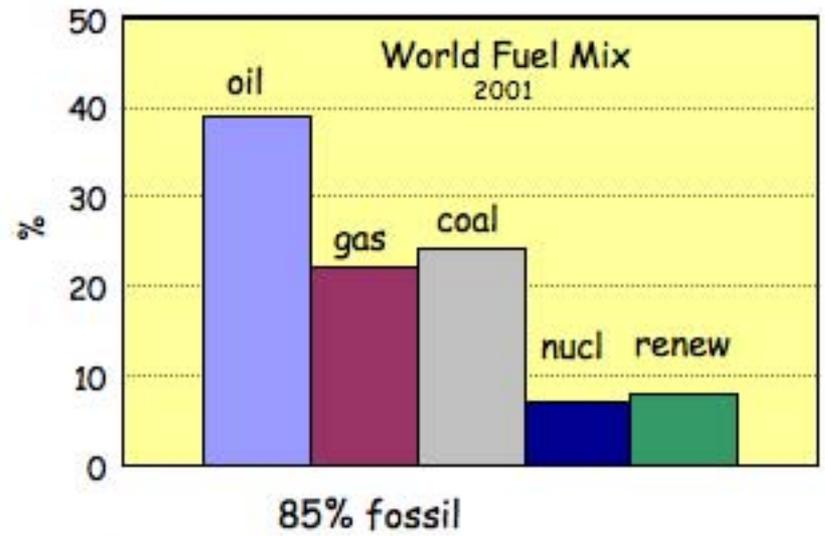


World Energy Demand

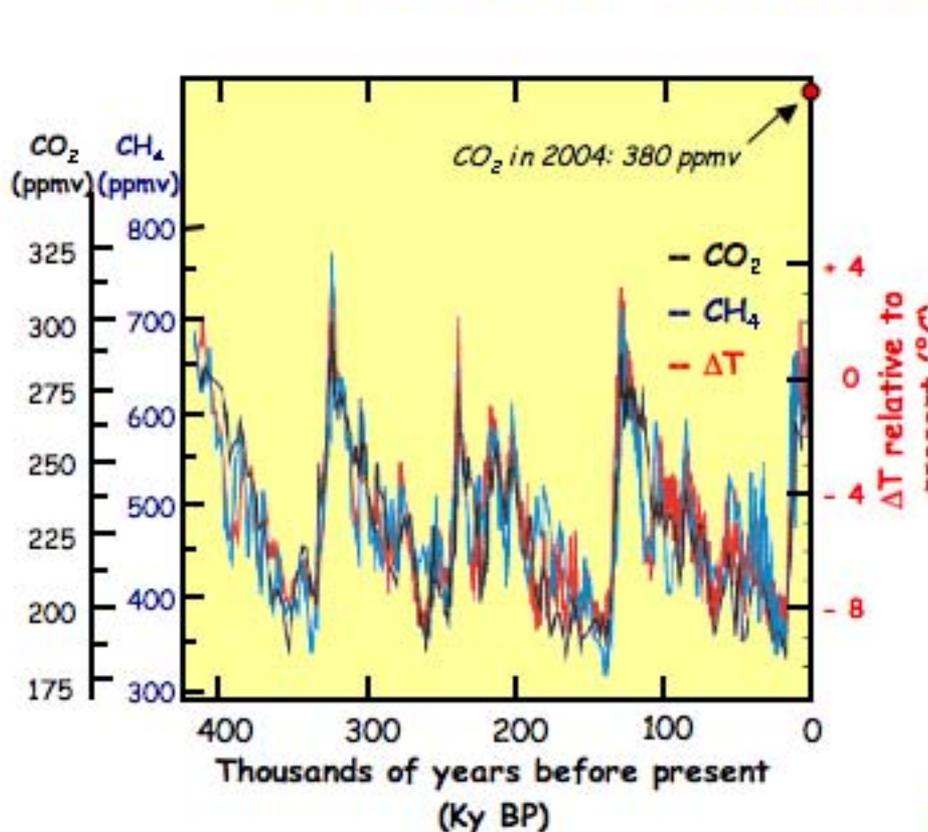


energy gap
~ 14 TW by 2050
~ 33 TW by 2100



EIA Intl Energy Outlook 2004
<http://www.eia.doe.gov/oiaf/ieo/index.html>
 Hoffert et al Nature 395, 883,1998

Fossil: Climate Change



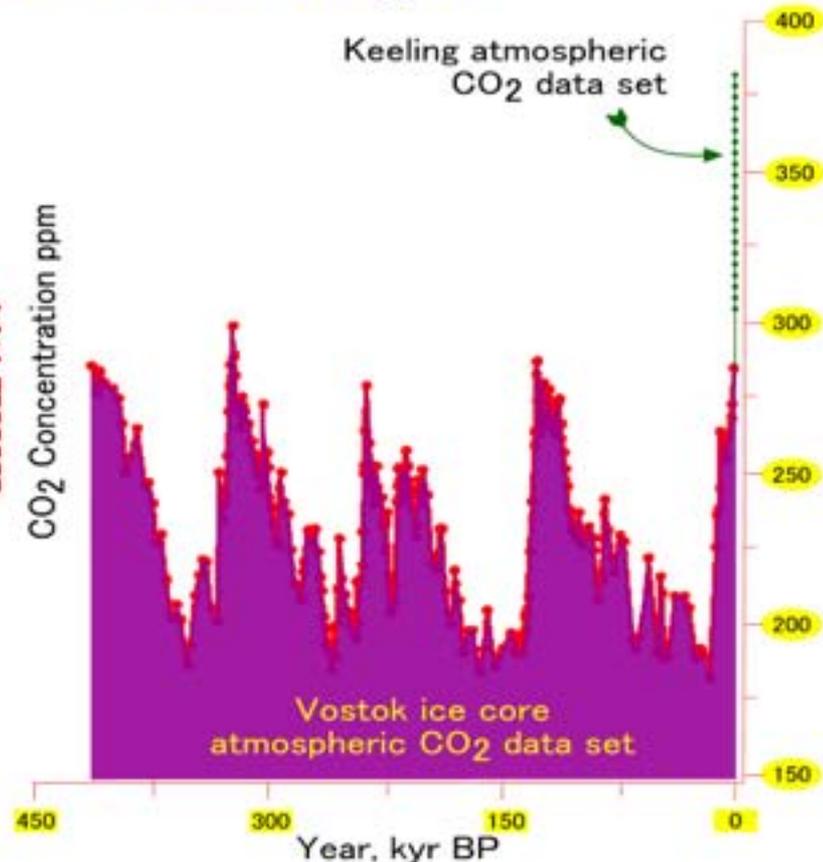
Climate Change 2001: The Scientific Basis, Fig 2.22

Intergovernmental Panel on Climate Change, 2001

<http://www.ipcc.ch>

N. Oreskes, Science 306, 1686, 2004

D. A. Stainforth et al, Nature 433, 403, 2005



Relaxation time

transport of CO₂ or heat to deep ocean: >3000 years

The Energy Gap

- ~ 14 TW of additional power by 2050
 - ~ 33 TW of additional power by 2100
- 2004 capacity: 13 TW

fossil energy

after oil production peaks, switch to gas and coal

capture/store 22 Gtonnes of CO_2 /yr (current emissions)

- 12,500 km³ at atmospheric pressure = volume of Lake Superior
 - 600 times CO_2 injected in oil wells/yr to spur production
 - 100 times the natural gas drawn in and out of geologic storage/yr to smooth demand
 - 20,000 times CO_2 stored/yr in Norway's Sleipner offshore reservoir
- ~~no leaks: 1% leak rate nullifies storage in 100 yrs~~

nuclear energy

14,000 1 GW_e fission reactors - 1 new reactor/day for 38 years

Renewable Energy

Solar

1.2×10^5 TW at Earth surface
600 TW practical

energy gap
~ 14 TW by 2050
~ 33 TW by 2100

Wind

2-4 TW extractable

Tide/Ocean Currents

2 TW gross

Geothermal

12 TW gross over land
small fraction recoverable



Biomass

5-7 TW gross
all cultivatable
land not used
for food

Hydroelectric

4.6 TW gross
1.6 TW technically feasible
0.9 TW economically feasible
0.6 TW installed capacity

Energy Conversion Strategies

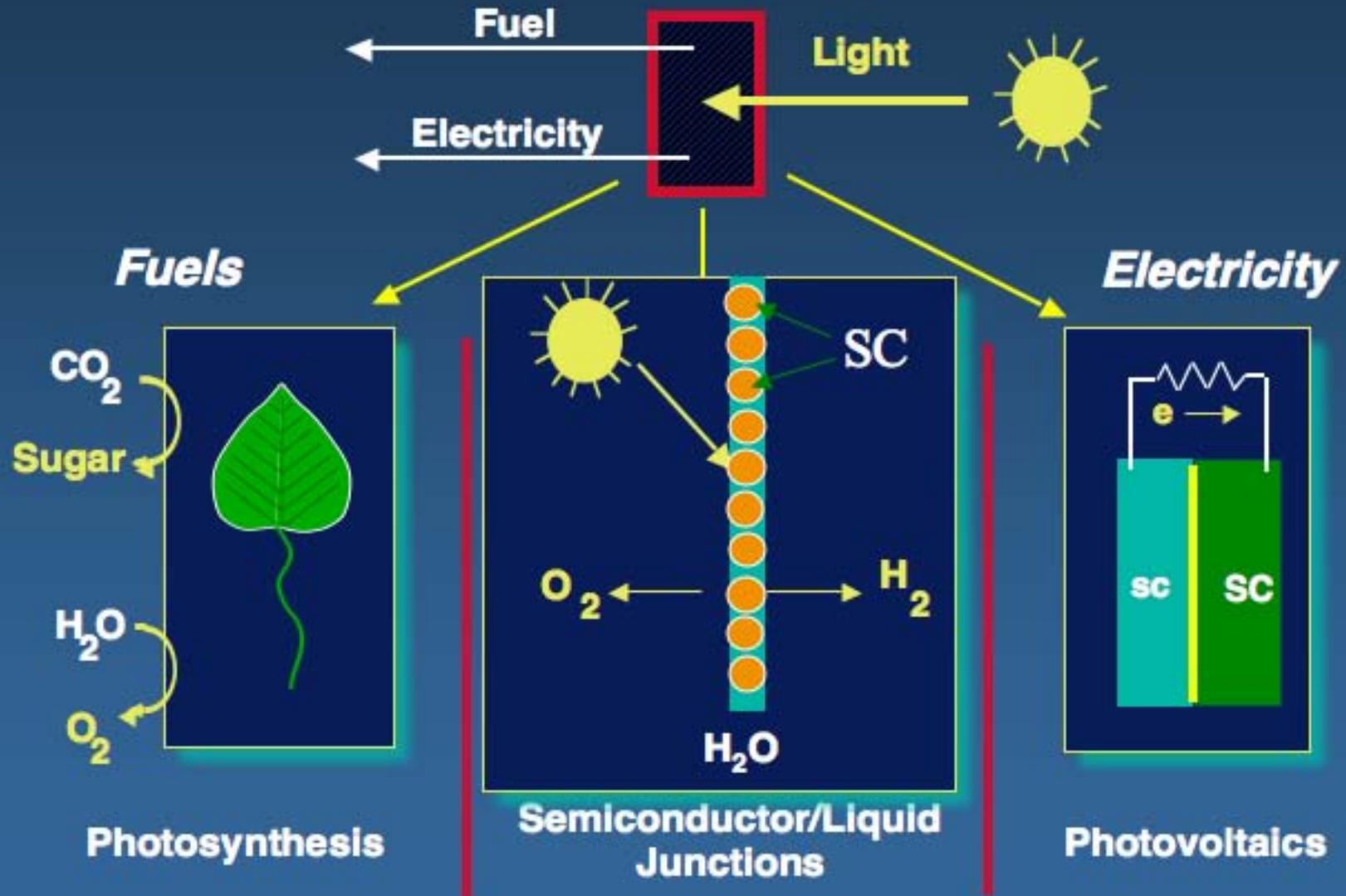


TABLE 5.14. CURRENT GLOBAL LAND-USE PATTERN

Cropland (arableland and permanent crops)		Forests and woodland		Permanent pastures		Other land			
						Total other land		Land with rainfed cultivation potential	
Gha	% of total	Gha	% of total	Gha	% of total	Gha	% of total	Gha	
1.5	11	4.2	21	3.4	26	4.0	31	1.6-1.8	

Note: Gha stands for billions of hectares. Total land availability is 13.1 billion hectares.

Source: FAO, 1995; 1999; Fisher and Hodge, 1998; WRI, 1998

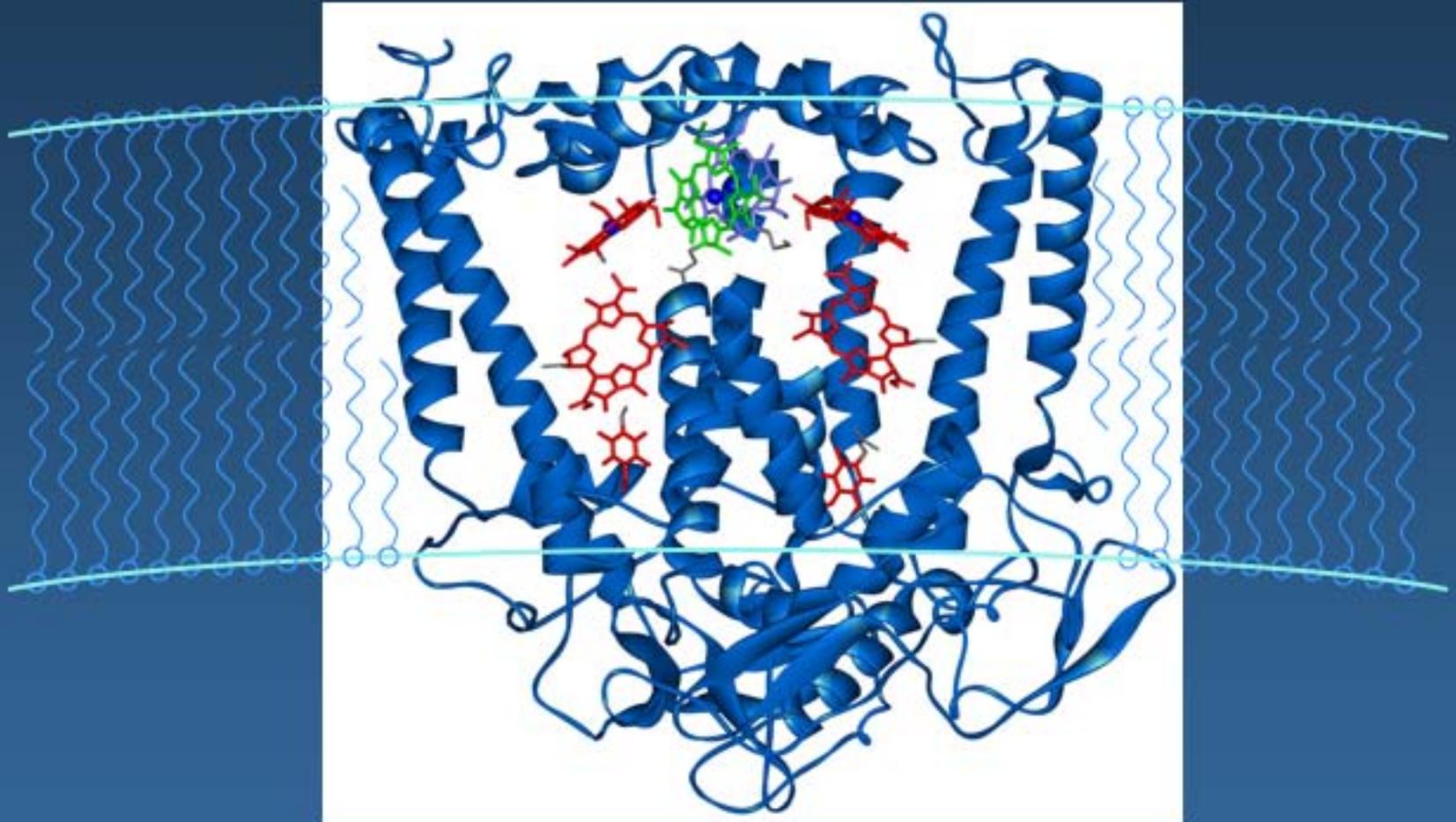
TABLE 5.15. PROJECTED BIOMASS ENERGY POTENTIAL, 2050 (BILLIONS OF HECTARES UNLESS OTHERWISE INDICATED)

1	2	3	4	5	6 ^a	7 ^b	7 ^c
Region	Population in 2050 (billions)	Land with crop produc- tion potential in 1990	Cultivated land in 1990	Additional cultivated land required in 2050	Maximum additional area for biomass production	Maximum additional amount of energy from biomass (exajoules)	
Industrialised countries ^d	-	-	0.670	0.050	0.100	17	30
Latin America							
Central and Caribbean	0.266	0.067	0.037	0.015	0.035	6	11
South America	0.524	0.865	0.153	0.082	0.830	107	189
Africa							
East	0.698	0.251	0.063	0.068	0.120	20	36
Central	0.264	0.363	0.043	0.052	0.288	49	86
North	0.317	0.164	0.040	0.014	0.060	9	15
Southern	0.106	0.044	0.016	0.012	0.016	3	5
West	0.639	0.196	0.090	0.096	0.010	2	3
Asia (excl. China)							
Western	0.367	0.042	0.037	0.010	-0.005	0	0
South-central	2.521	0.200	0.205	0.021	-0.026	0	0
East	1.722	0.175	0.131	0.008	0.036	6	11
South-east	0.812	0.148	0.082	0.038	0.028	5	8
China	-	-	-	-	-	2 ^e	2 ^e
Total^f	8.296	2.495	0.897	0.416	1.28	226	396
Global biomass energy potential						276^g	446^g

a. (6) = (3) - (4) - (5). b. (7) = (6) x 8.5 [oven dry tonnes a hectare per year] x 20 [GJ per oven dry tonne] based on higher heating value (18 GJ per oven dry tonne for lower heating value). The assumptions for biomass productivity may appear on the high side, but they represent technically achievable yields given dedicated research, development, and dissemination. c. (7) = (6) x 15 [oven dry tonnes a hectare per year] x 20 [GJ per oven dry tonne] based on higher heating value (18 GJ per oven dry tonne for lower heating value). d. OECD, Central and Eastern Europe, newly independent states of the former Soviet Union. e. Data are projected values from d'Agosta (1998), not maximum estimates. f. Totals in (2), (3), (4), and (5) exclude industrialised countries. g. Includes 50 EJ of current biomass energy generation.

Source: Derived from Fisher and Hodge, 1998; d'Agosta, 1998; Nairnwood, Graham, and McDonald, 1998

Bacterial Photosynthetic Reaction Center



rhodobacter sphaeroides

Stowell, M.H.B.; Rees, D.C.; et. al. *Science* 1997, 276, 882.

photons in
1 oxidant & reductant out

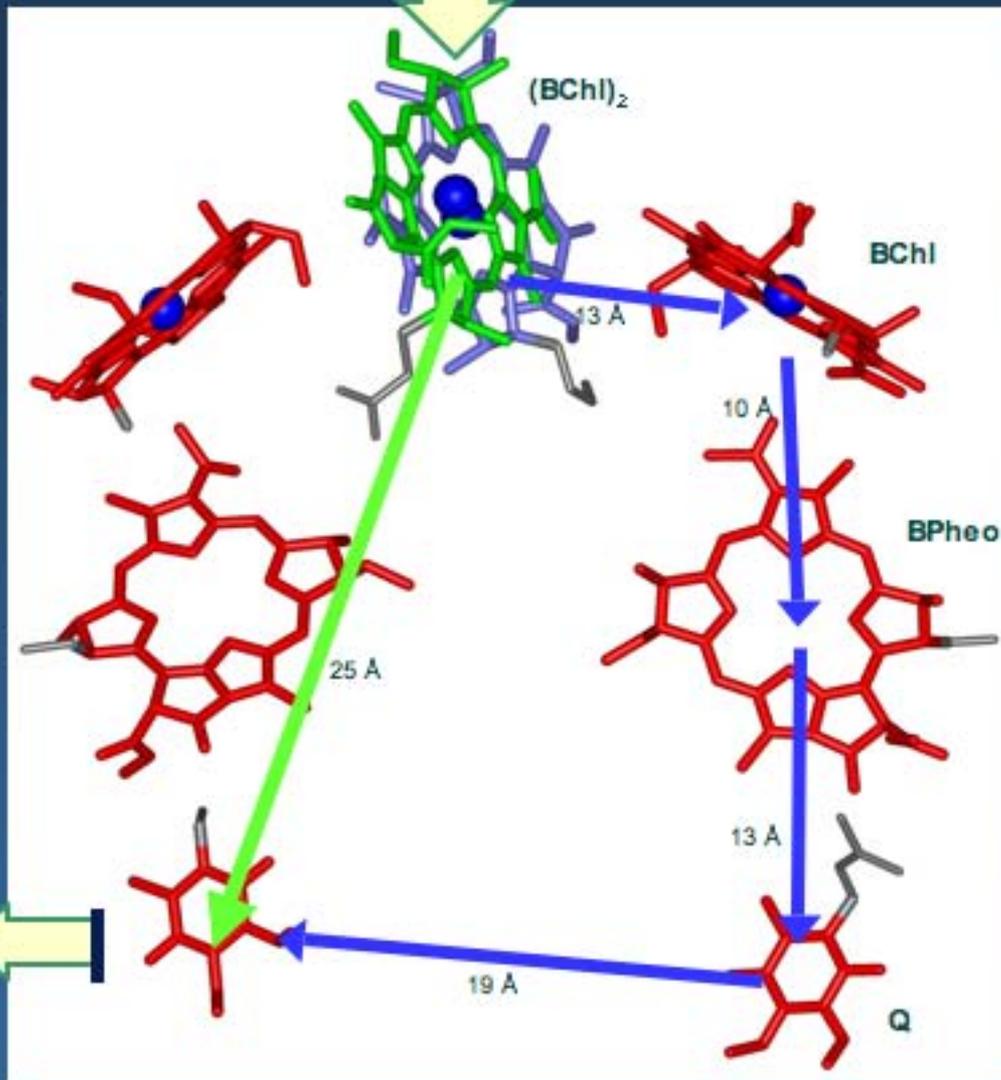
Energy In

BChl bacteriochlorophyll
BPheo bacteriopheophytin
Q quinone

1 step distance : 25 Å
calculated time : ~100 ps

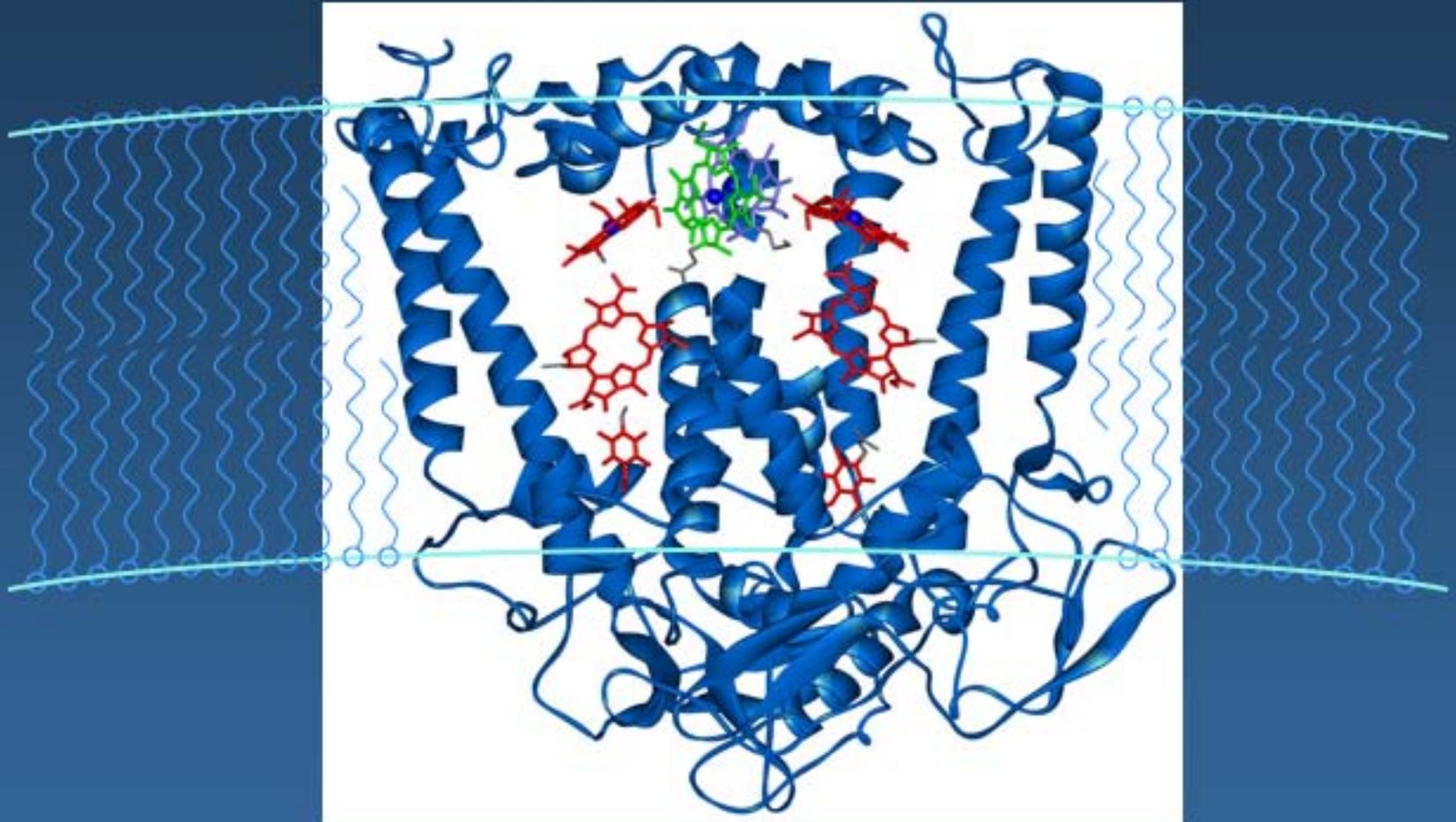
4 steps
ET distance : 55 Å
total time : < 1 ns

reducing
equivalents



Boxer, S.G. *Annu. Rev. Biophys. Biophys. Chem.* 1990, 19, 267.

Bacterial Photosynthetic Reaction Center



rhodobacter sphaeroides

photons in
1 oxidant & reductant out

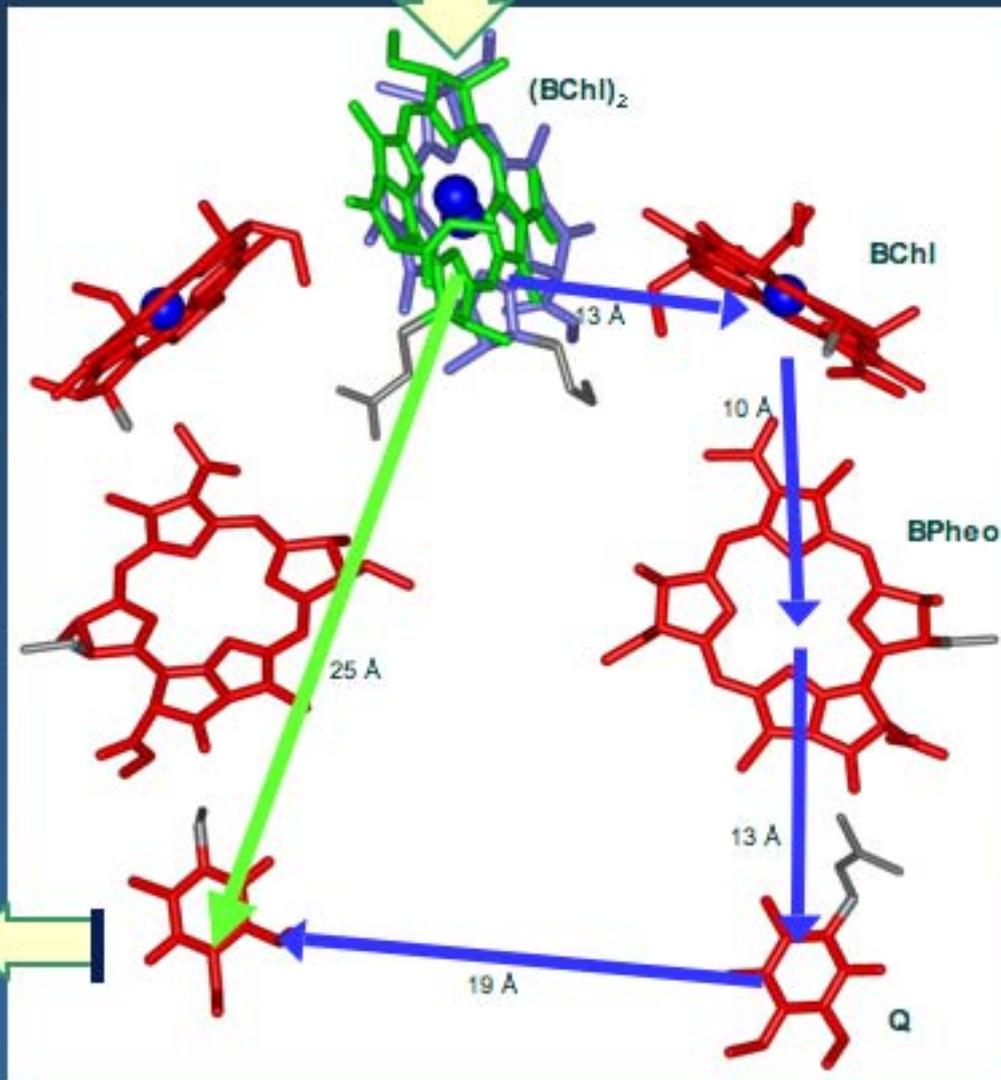
Energy In

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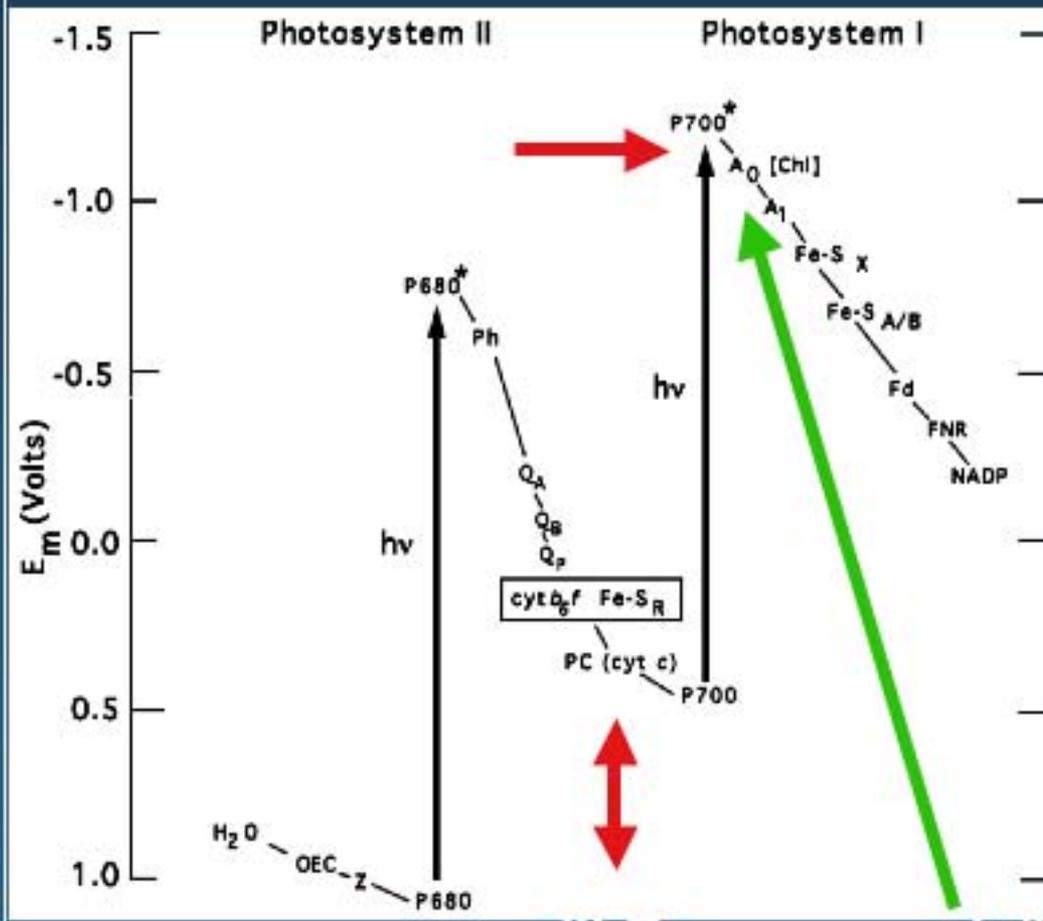
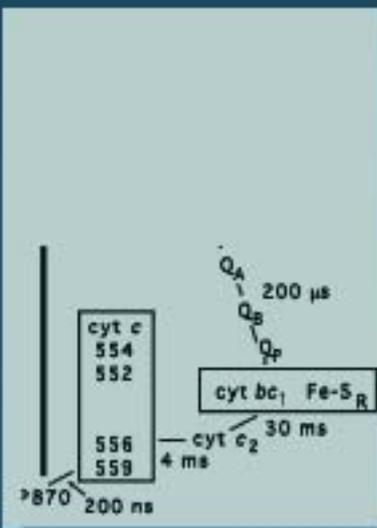
reducing
equivalents



Boxer, S.G. *Annu. Rev. Biophys. Biophys. Chem.* 1990, 19, 267.

ature uses two photosystems to span the redox space from O_2/H_2O to $NAD^+/NADH$

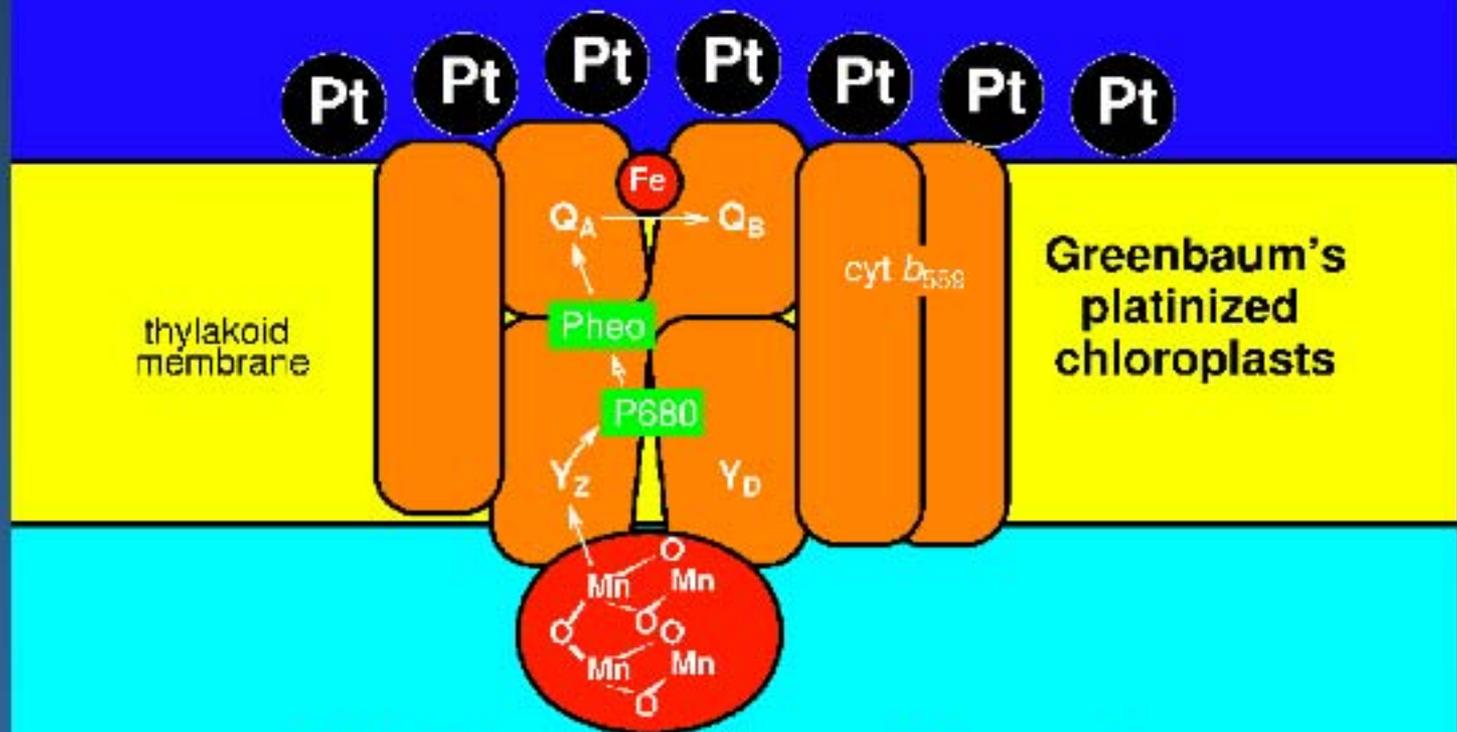
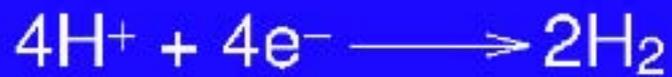
Purple Bacteria



N.B.

Giving more thermodynamic push to synthesis

Thanks to B Blankenship

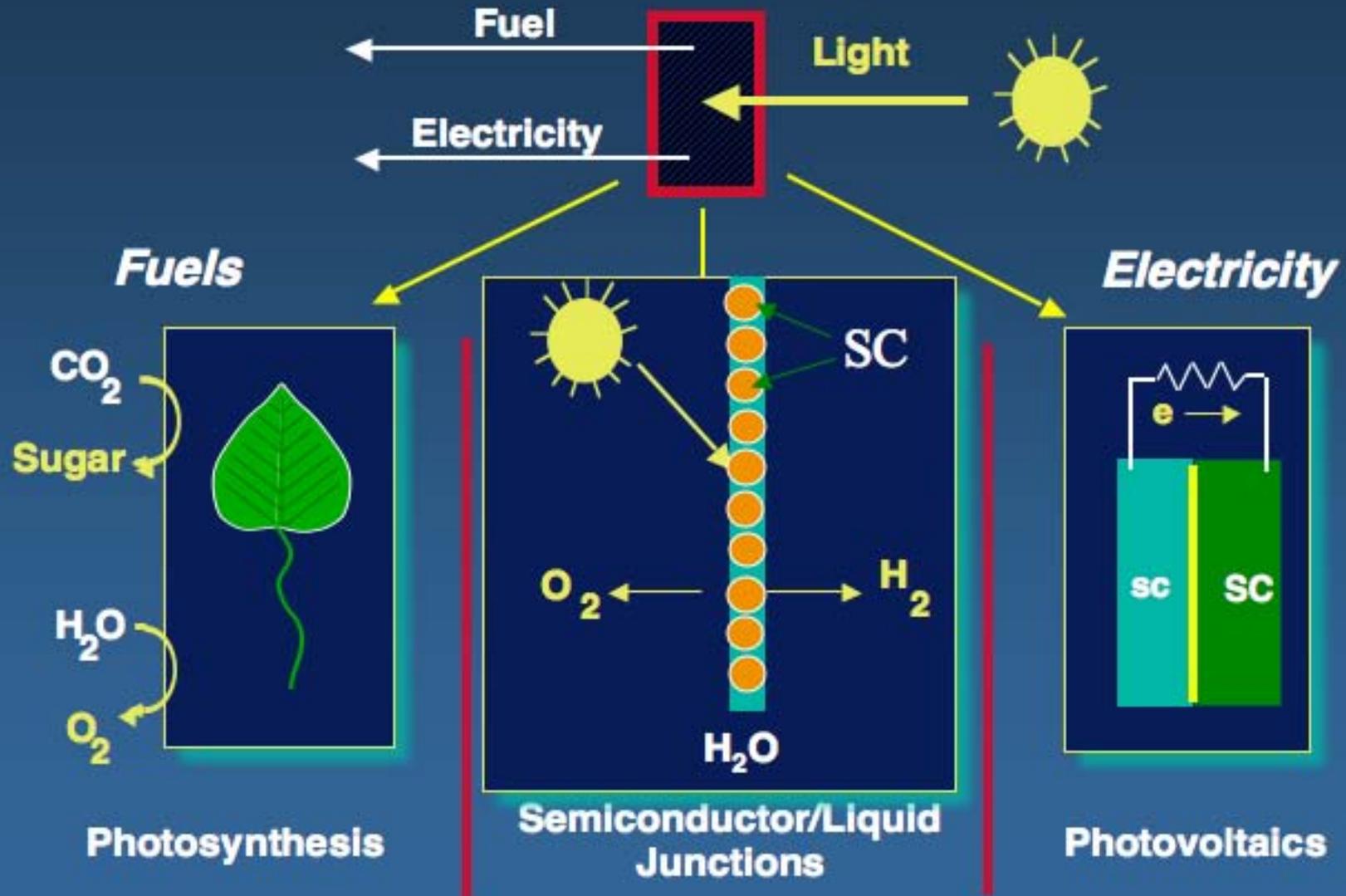


Greenbaum's
platinized
chloroplasts

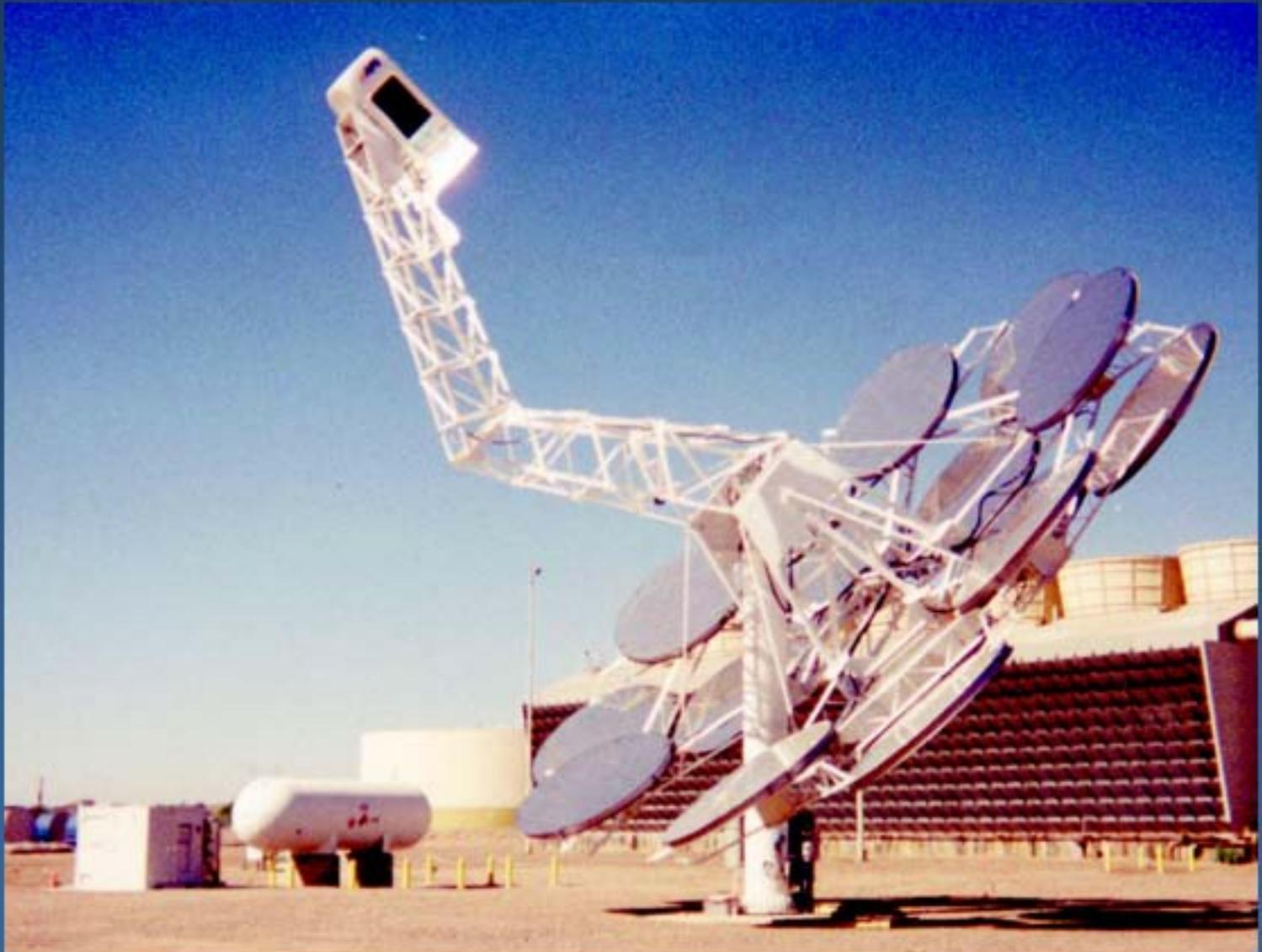
thylakoid
membrane



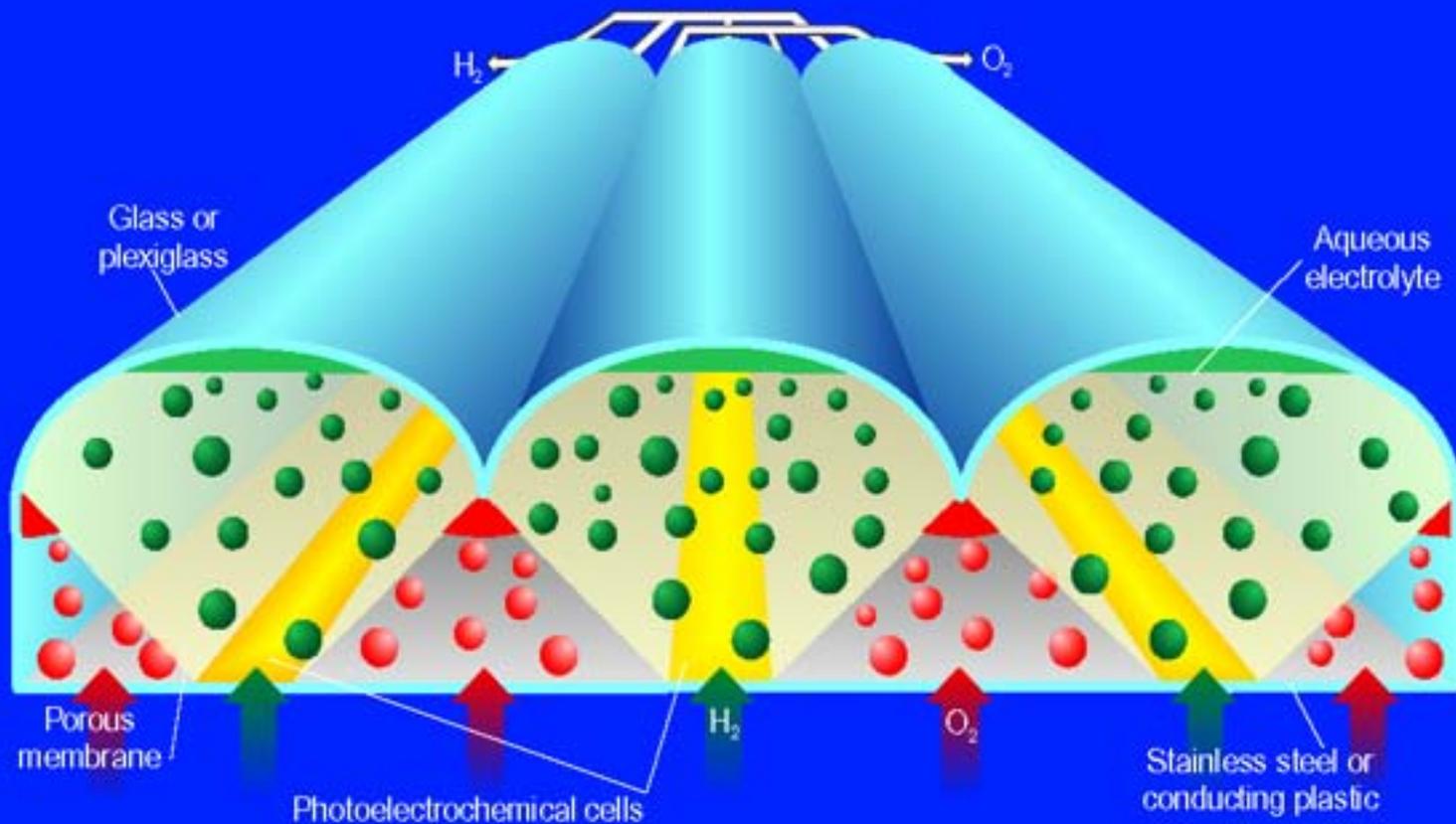
Energy Conversion Strategies



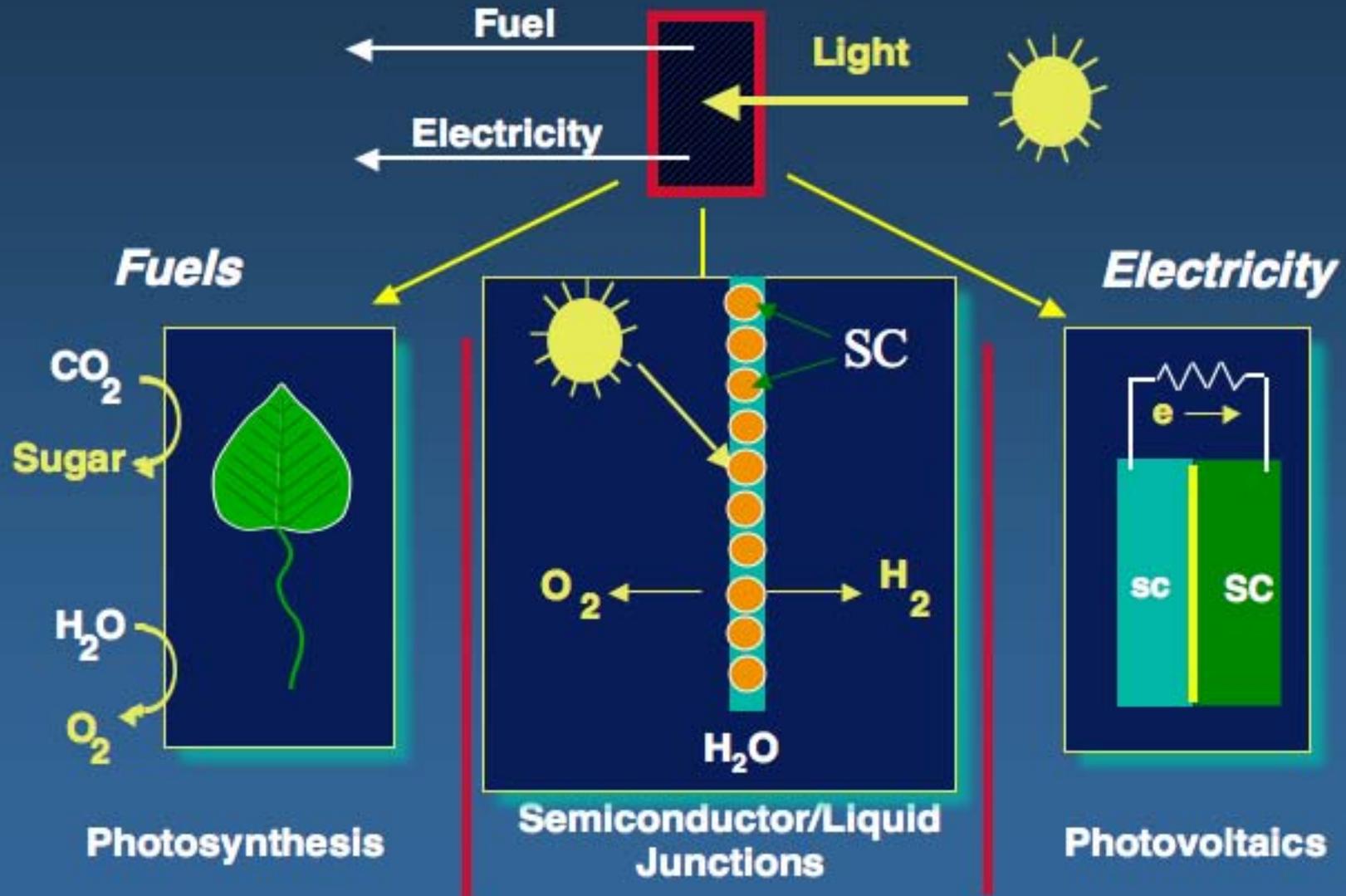
Photovoltaic + Electrolyzer System



Photoelectrolysis System



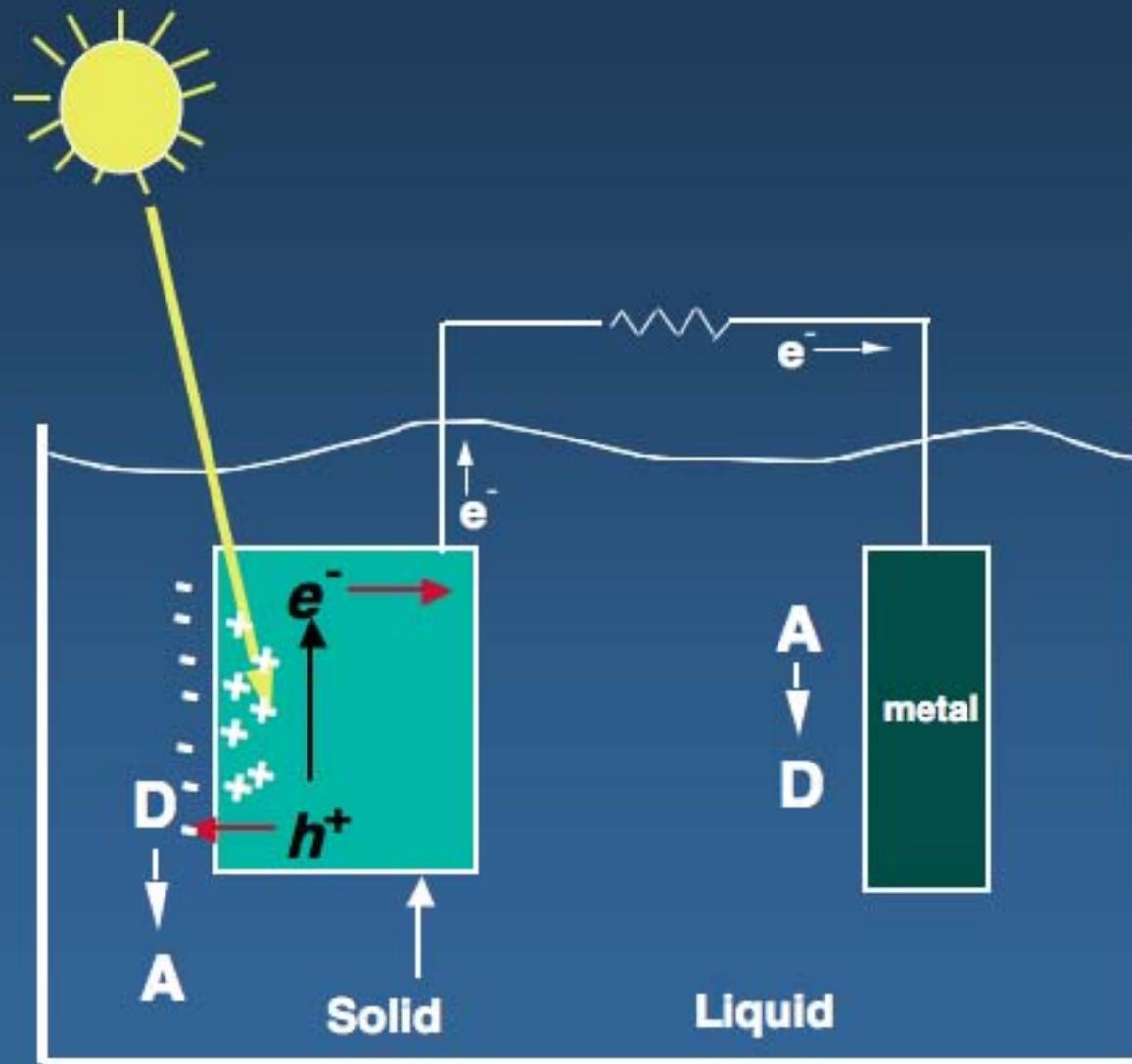
Energy Conversion Strategies



Fuel from Sunlight

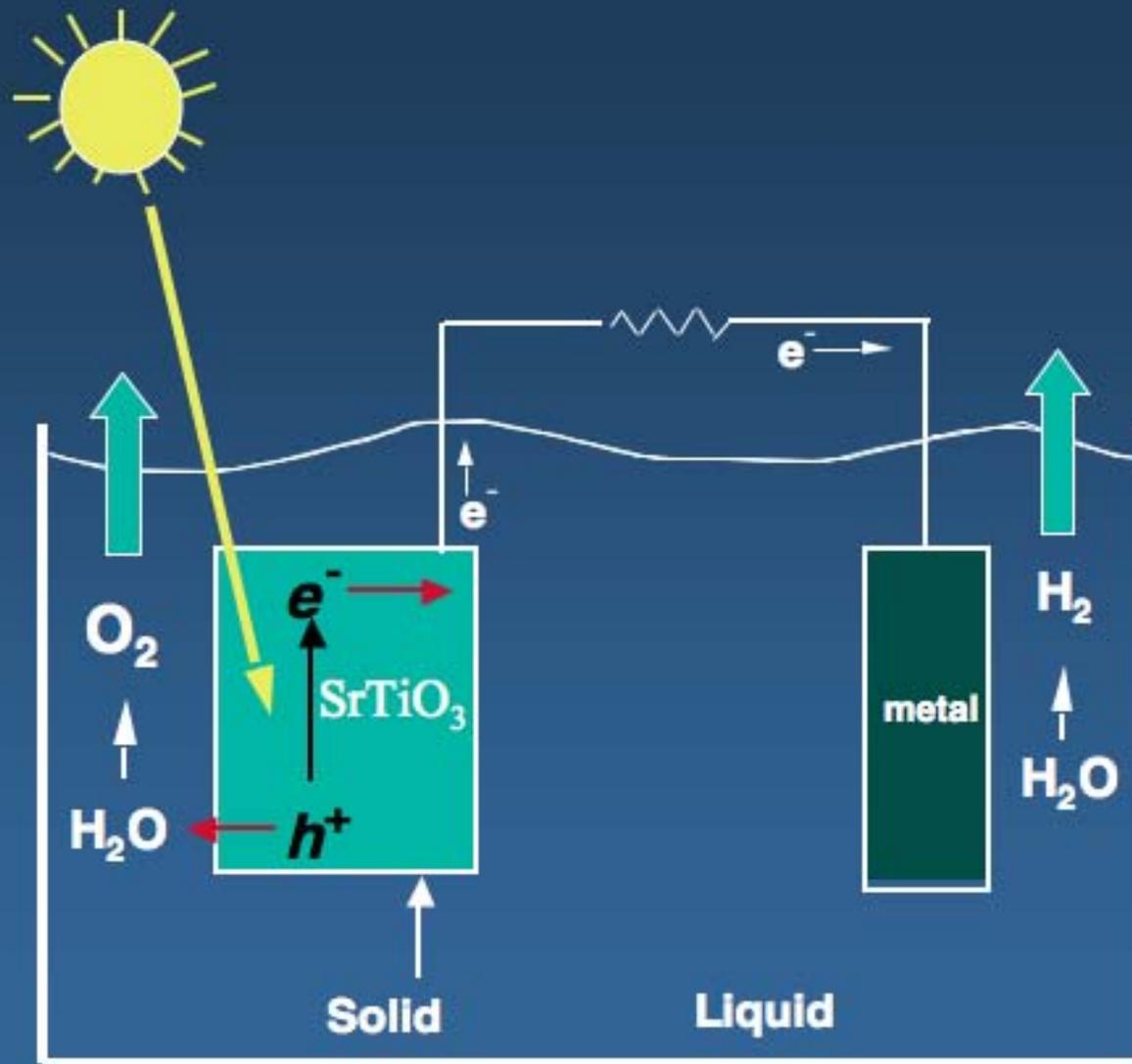


Photoelectrochemical Cell



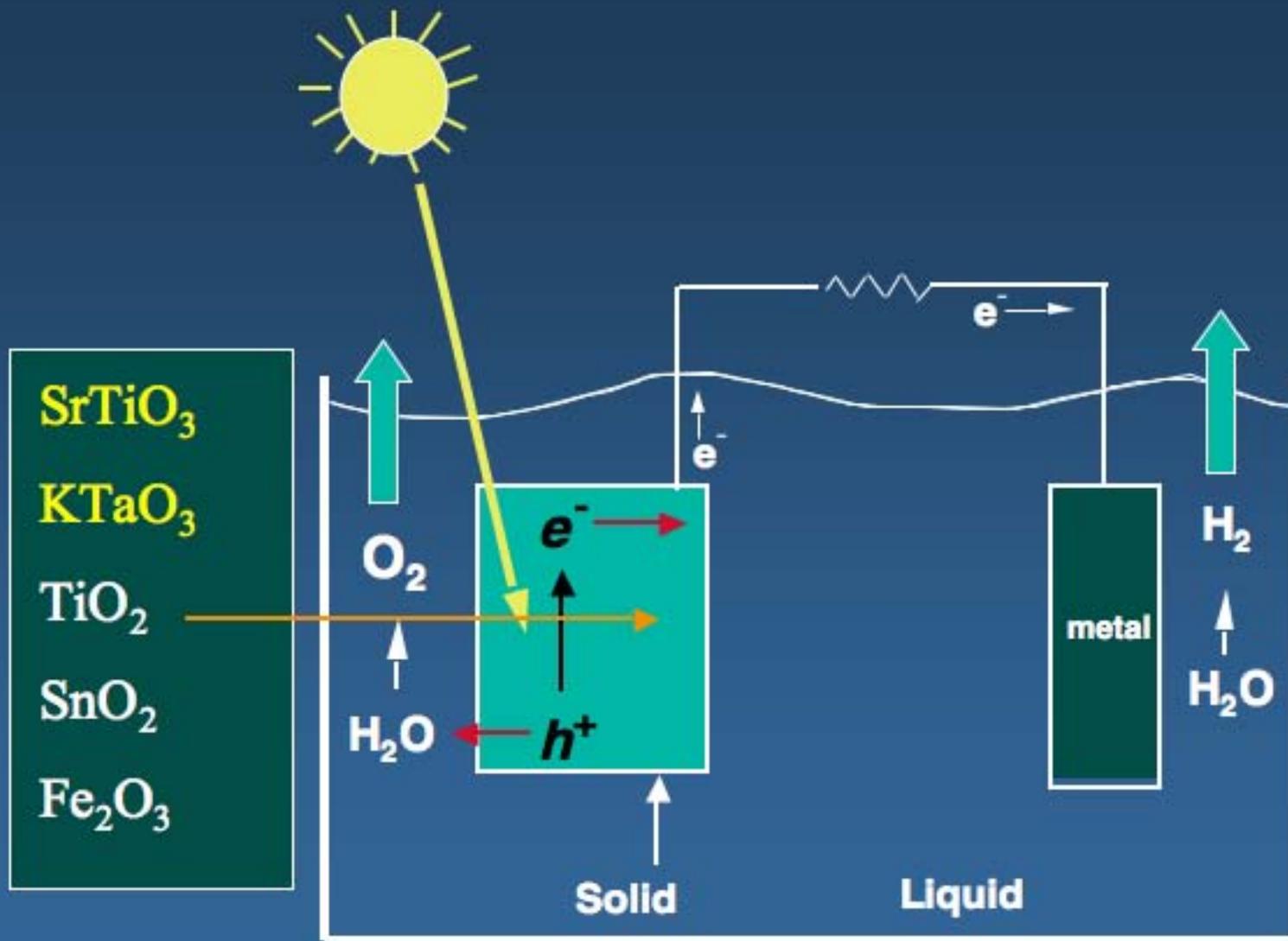
Light is Converted to Electrical+Chemical Energy

Photoelectrochemical Cell



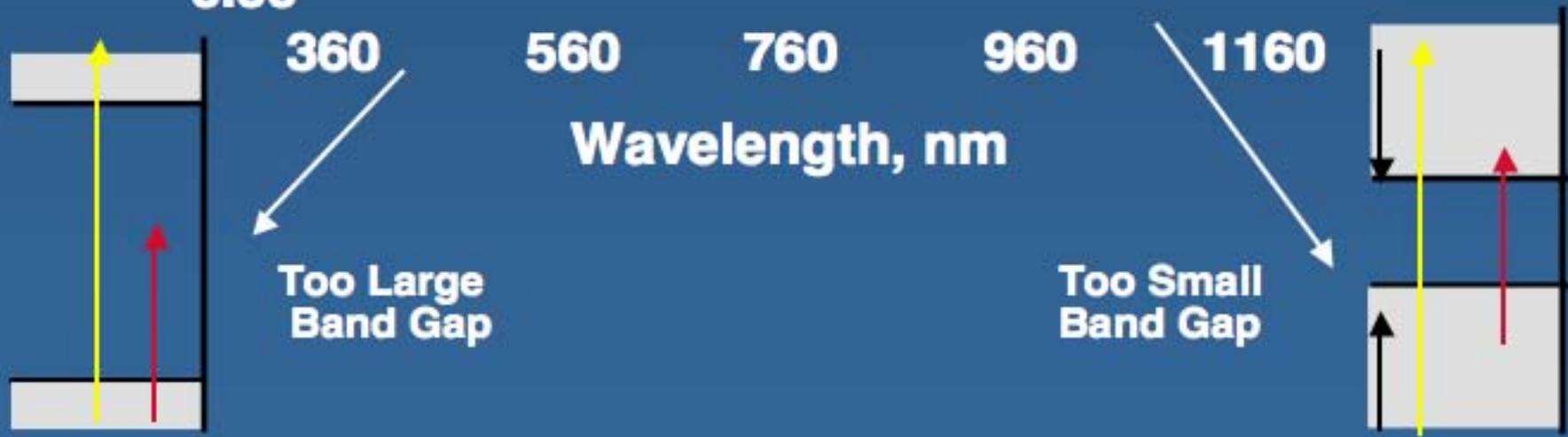
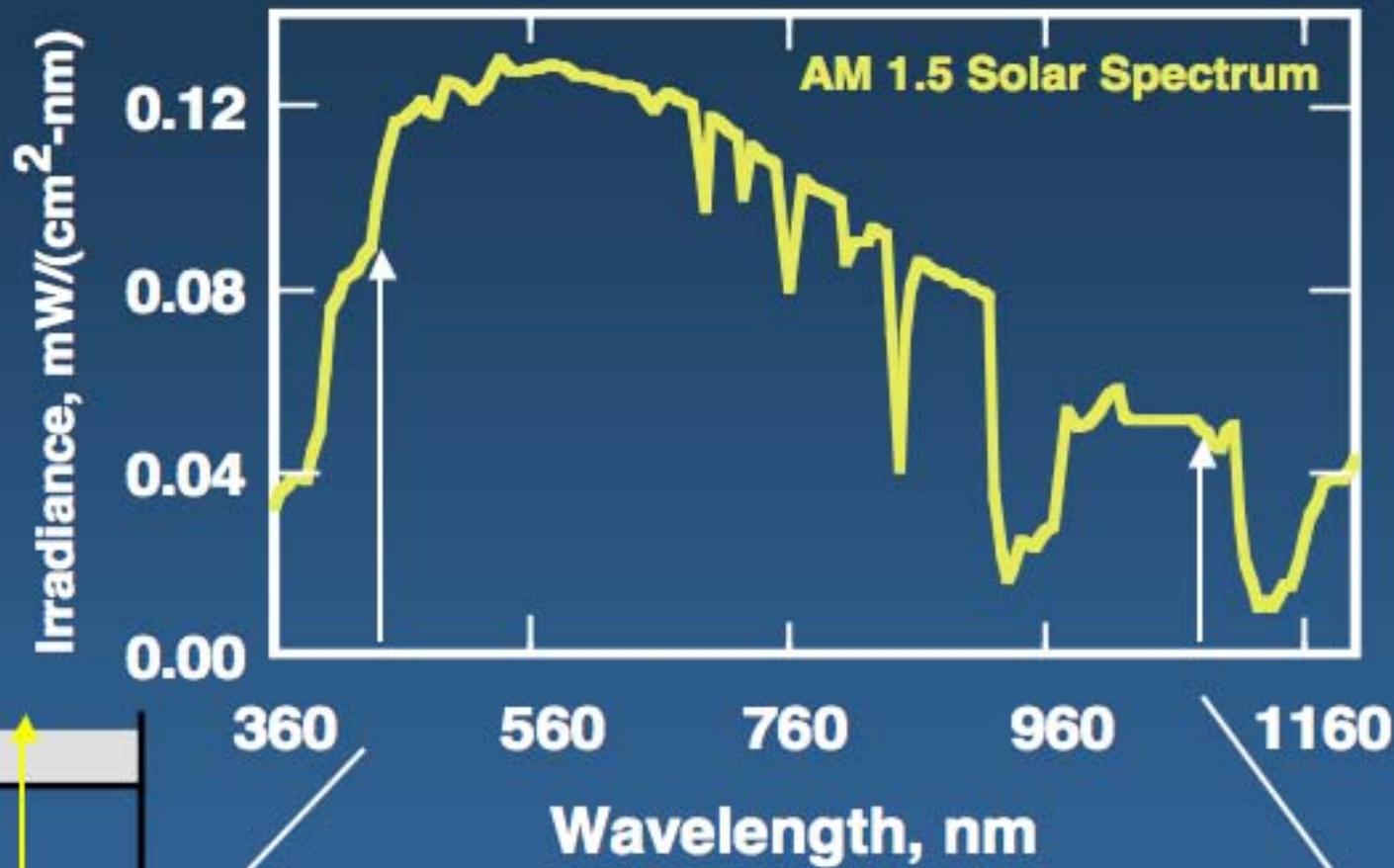
Light is Converted to Electrical+Chemical Energy

Photoelectrochemical Cell



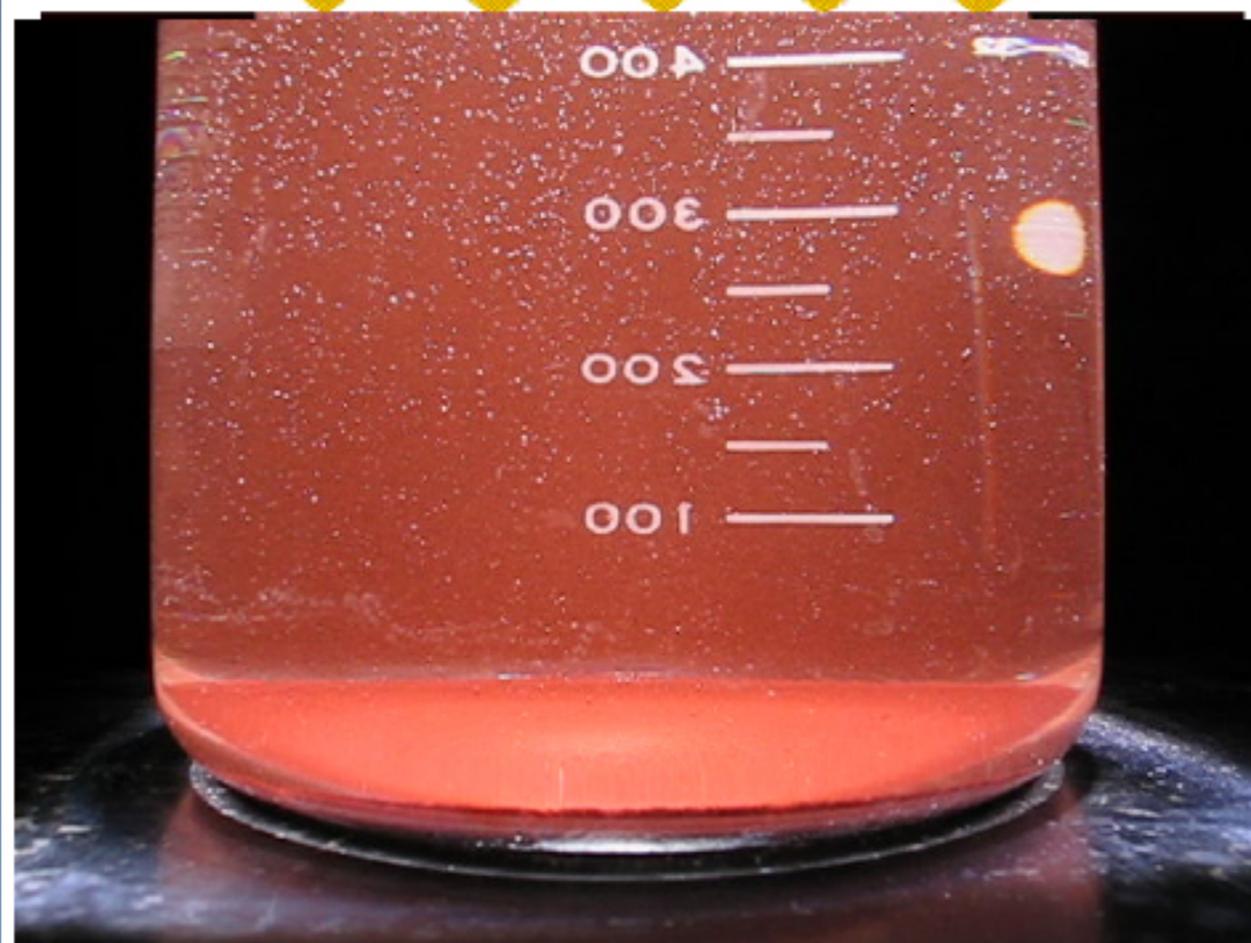
Light is Converted to Electrical+Chemical Energy

Optimum Absorption Threshold



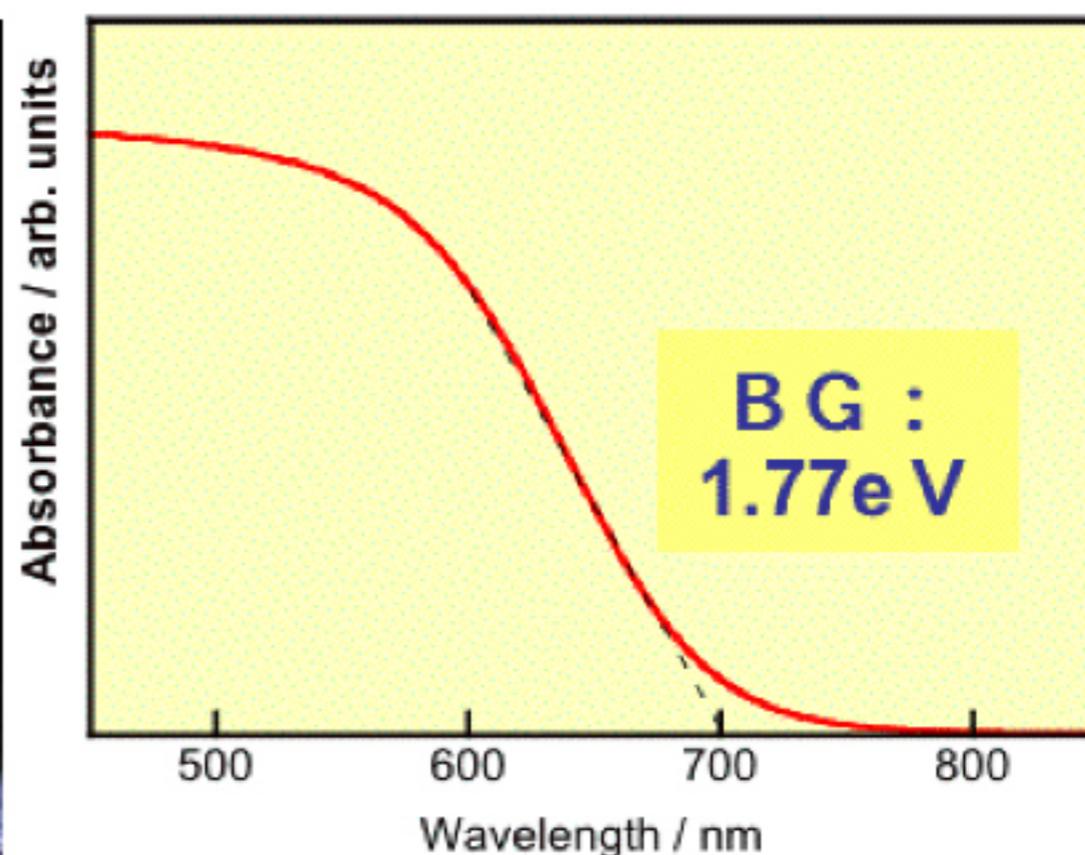
Solar H₂ production on Ru/CuInS₂-AgInS₂-ZnS solid solution photocatalyst

Solar simulator(AM-1.5)

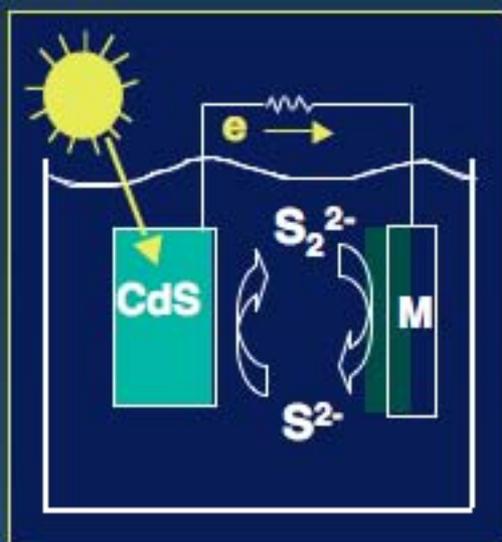


Photocatalyst Reactant: K₂SO₃ + Na₂S

Rate of H₂ evolution
8L/h·m²

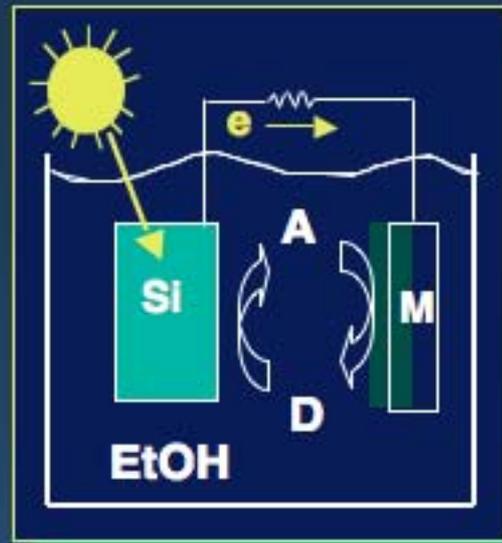


I. Tsuji, H. Kato, and A. Kudo,
Angew. Chem., Int. Ed., 44, 3565 (2005), *Chem. Mater.*, 18, 1969 (2006).

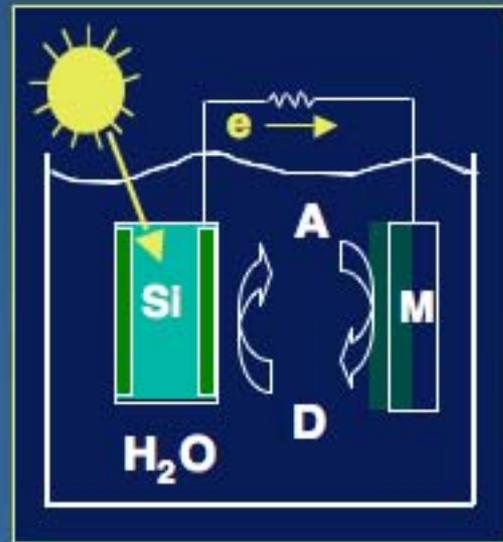


New Redox Couples

Nonaqueous Solvents

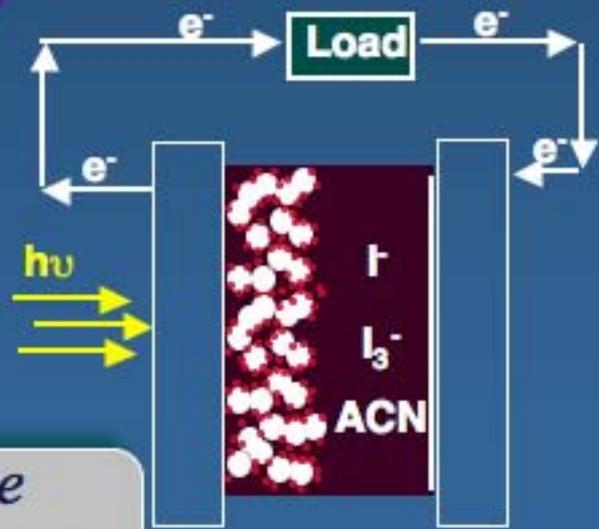


Four Strategies



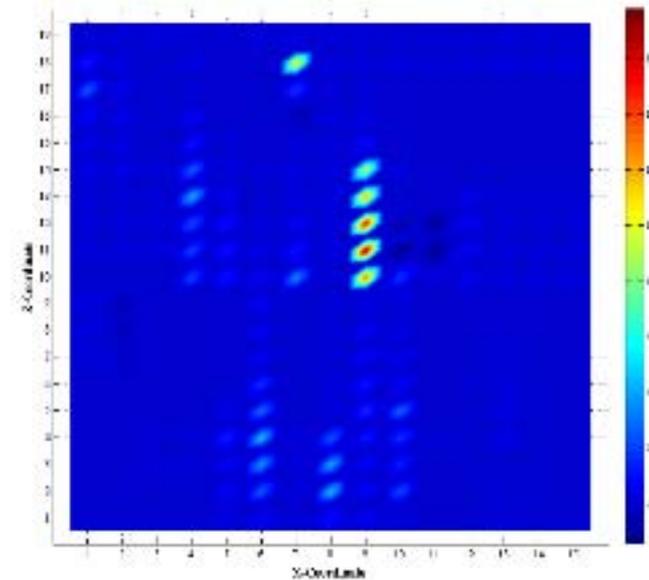
Surface Modification

Inexpensive Semiconductors



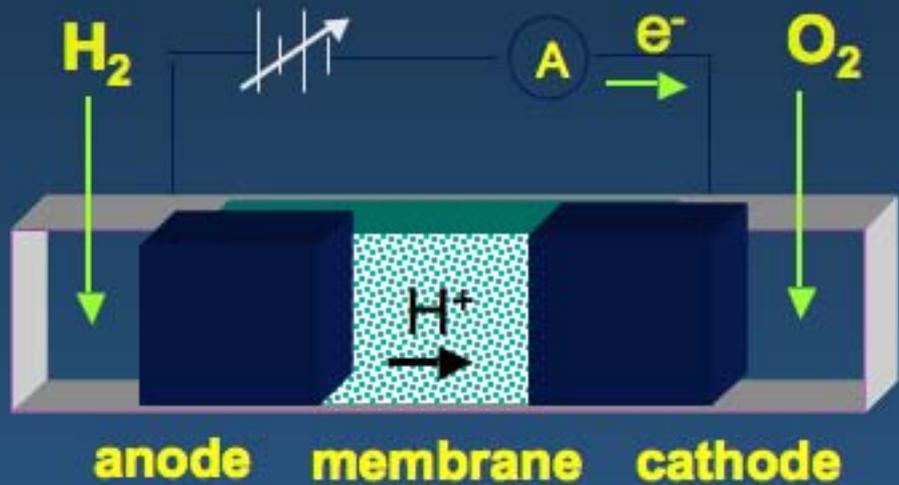


FTO slide printed with binary combinations of eight metals, pyrolyzed to form mixed metal oxides.

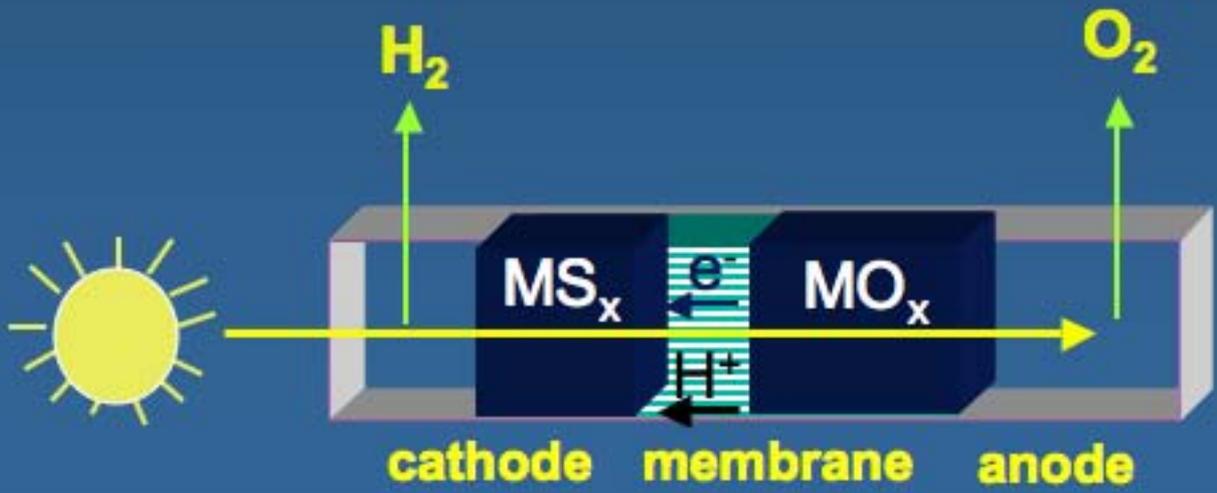


Typical photocurrent map of a slide of metal oxides. The X- and Z-coordinates give each spot's identity, which is correlated with photo-catalytic activity. Here, combinations of Zn and Co in row #9 show photoanodic current

Fuel Cell vs Photoelectrolysis Cell



Fuel Cell
MEA



Photoelectrolysis
Cell MEA



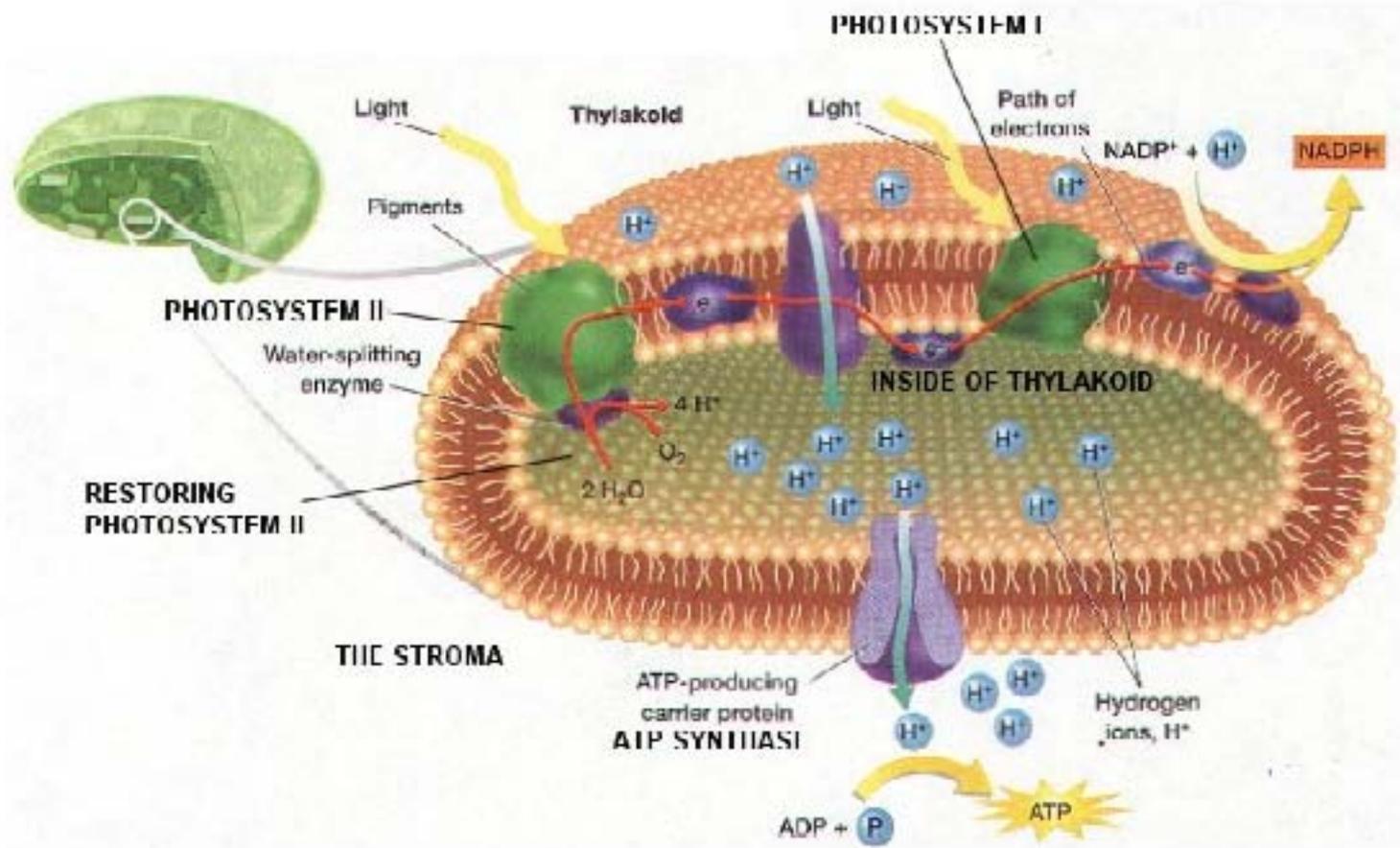
Towards a Solar Fuels System



M. Calvin, 1982: It is time to build an actual artificial photosynthetic system, to learn what works and what doesn't work, and thereby set the stage for making it work better

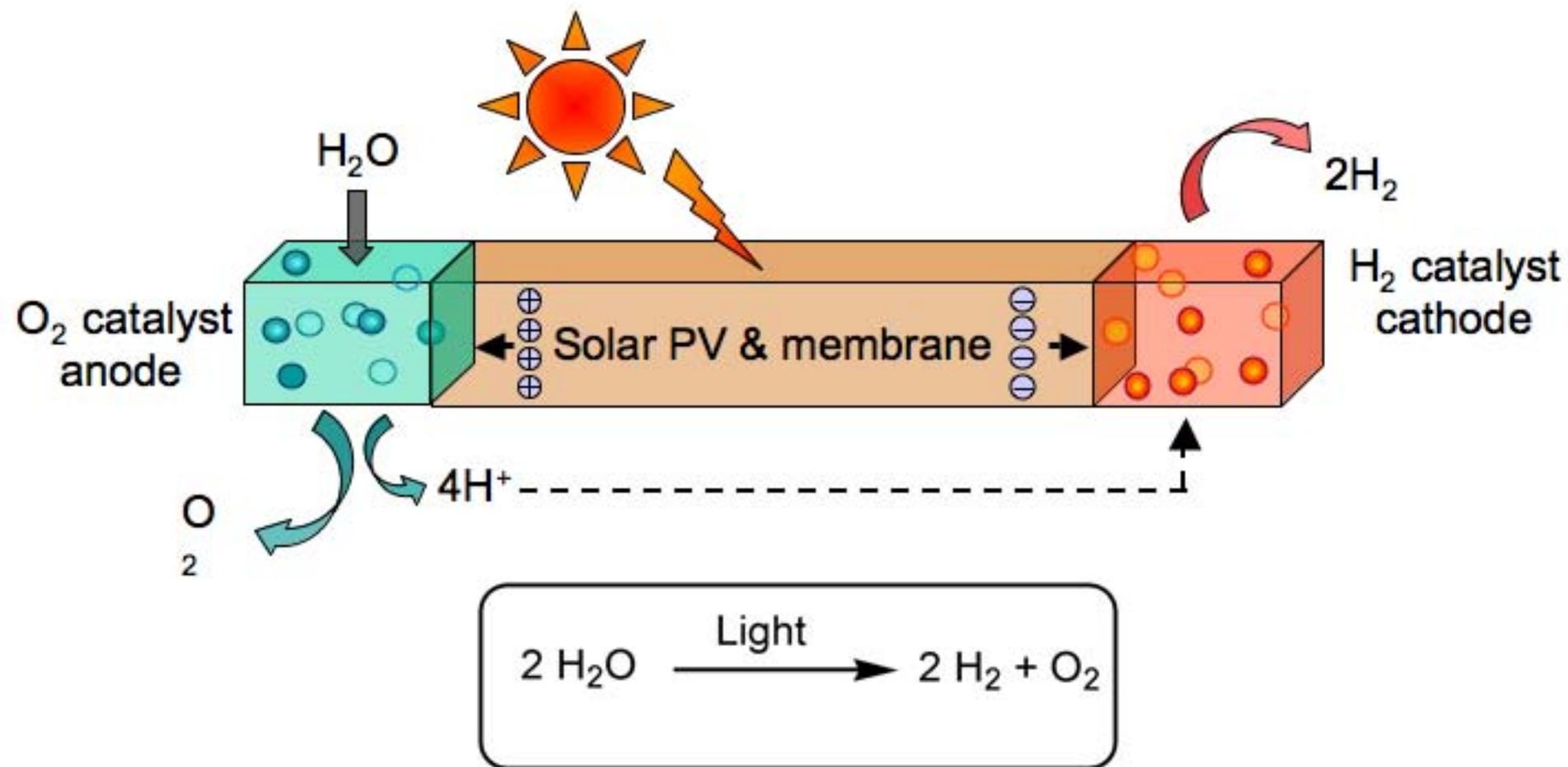
2007 Goal: To demonstrate a manufacturably scalable solar fuel generator, using earth-abundant elements, that, with no wires, robustly produces fuel from the sun, 10 times more efficiently than (current) crops

Lessons from Photosynthesis

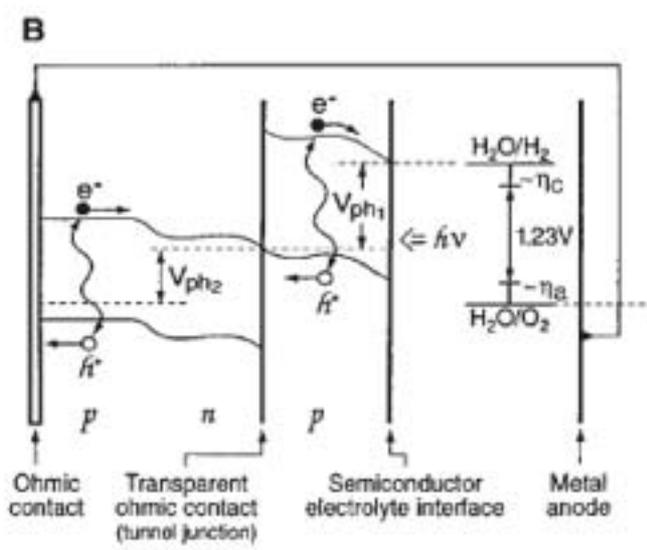
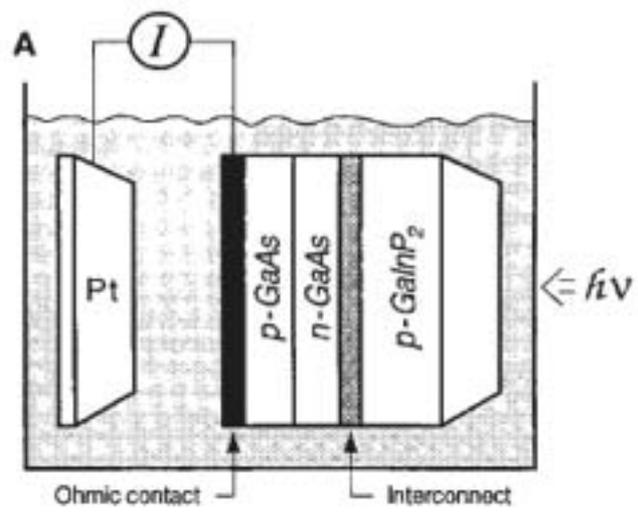




System Concept

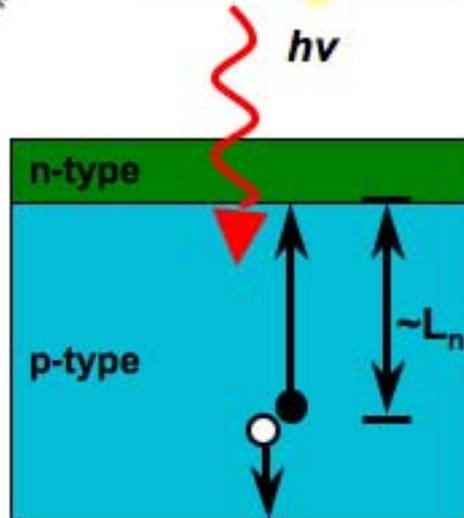


Turner Cell





Why Radial Junction Solar Cells?

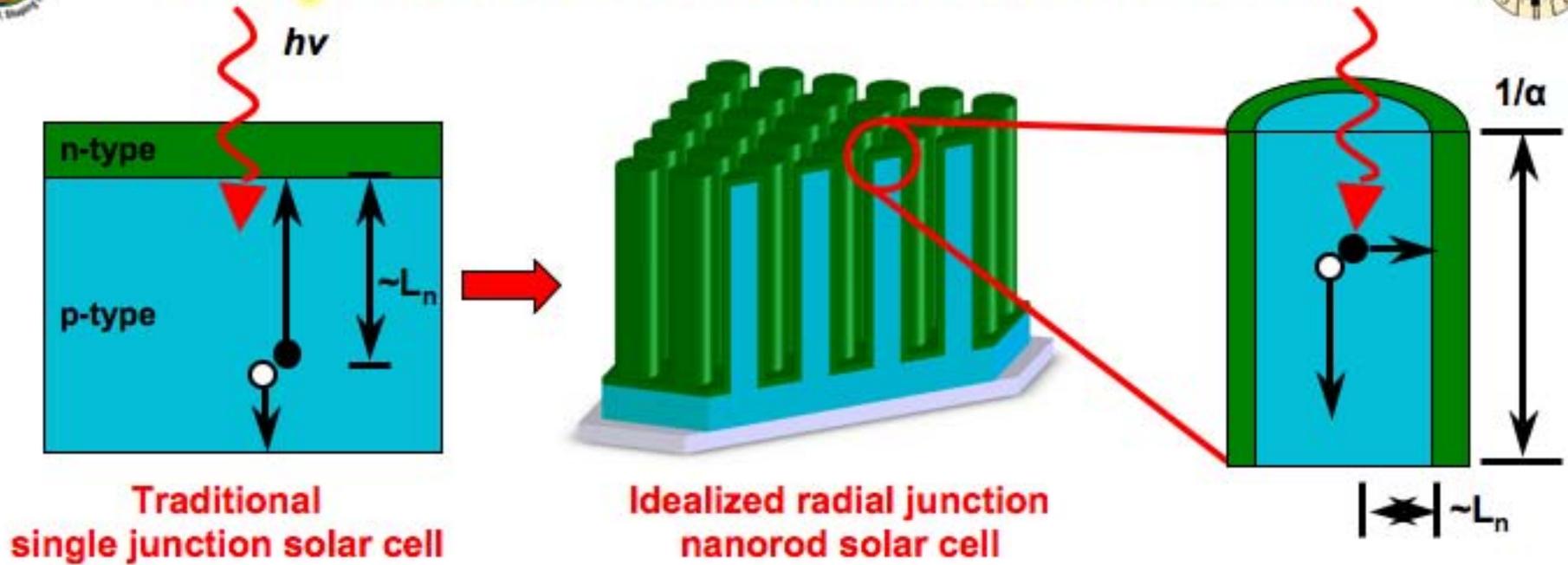


**Traditional
single junction solar cell**

- Traditional device design requires long minority carrier diffusion lengths, and therefore expensive materials



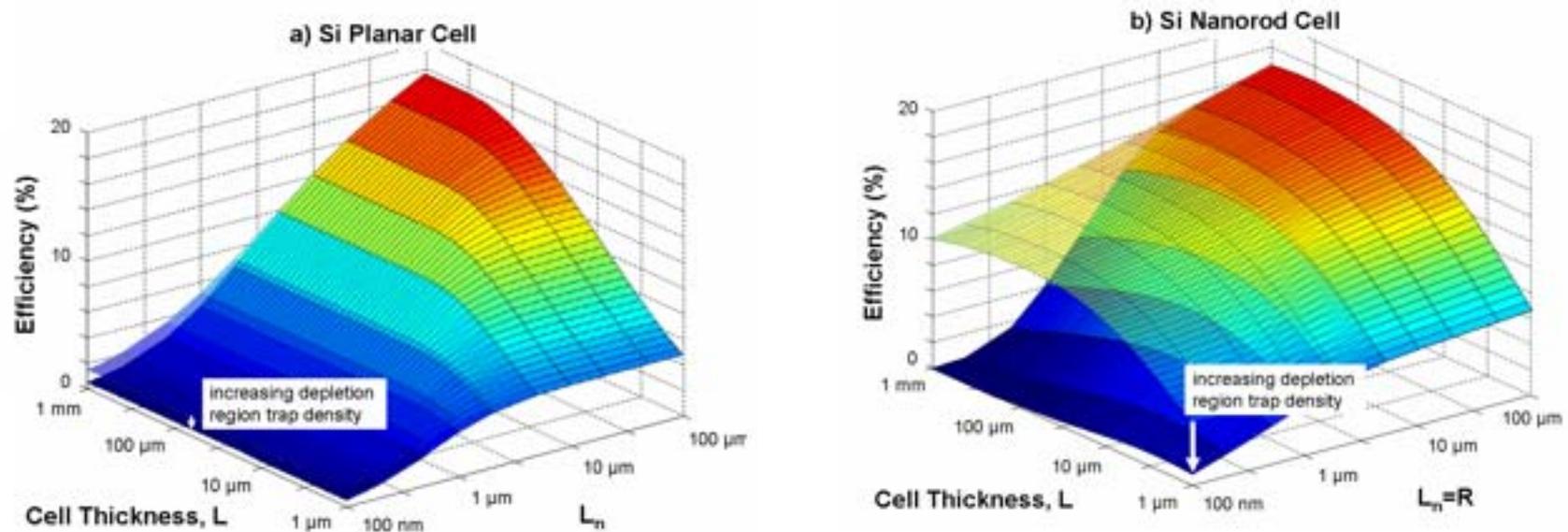
Why Radial Junction Solar Cells?



- Traditional device design requires long minority carrier diffusion lengths, and therefore expensive materials
- **Radial geometry allows for high quantum efficiency despite short minority carrier diffusion lengths**



Device Modeling

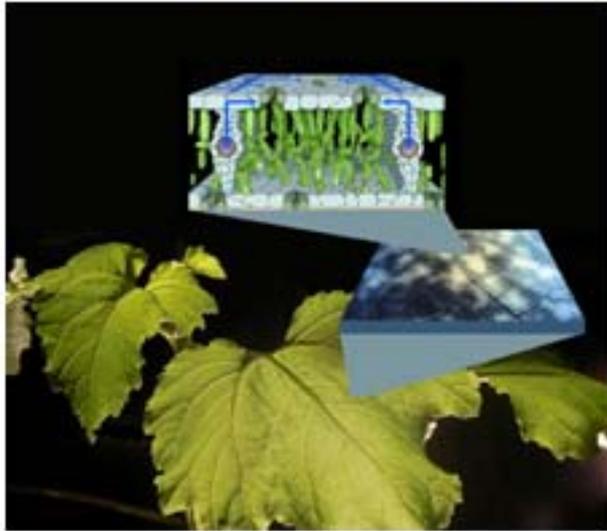


Comparison of photovoltaic efficiency for (a) planar and (b) nanowire Si devices as a function of absorber thickness and minority carrier diffusion length

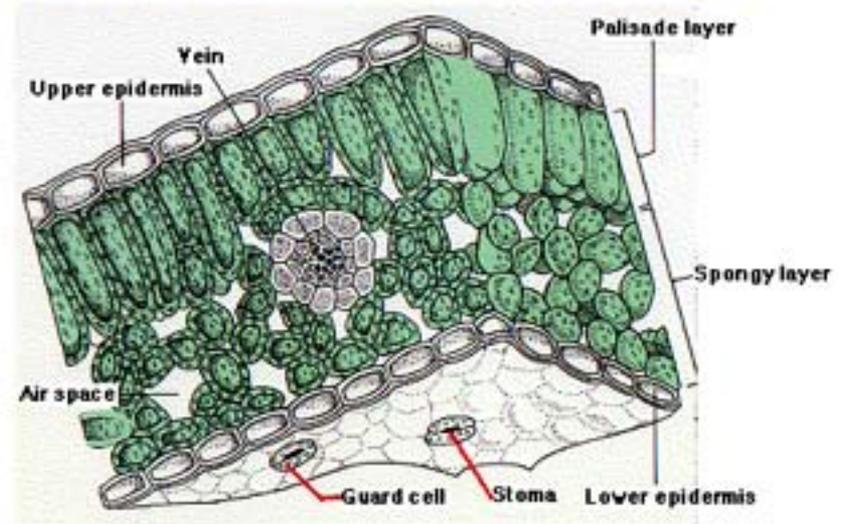
Relatively high efficiencies possible despite low diffusion lengths if depletion region recombination can be minimized

B.M. Kayes, H. A. Atwater, and N. S. Lewis, *J. Appl. Phys.* 97 114302 (2005)

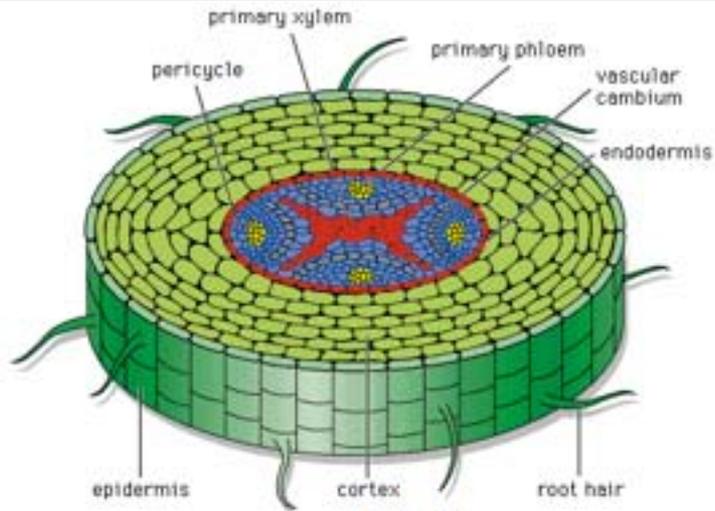
Structural Organization in Nature



Stomata



Leaf



Root

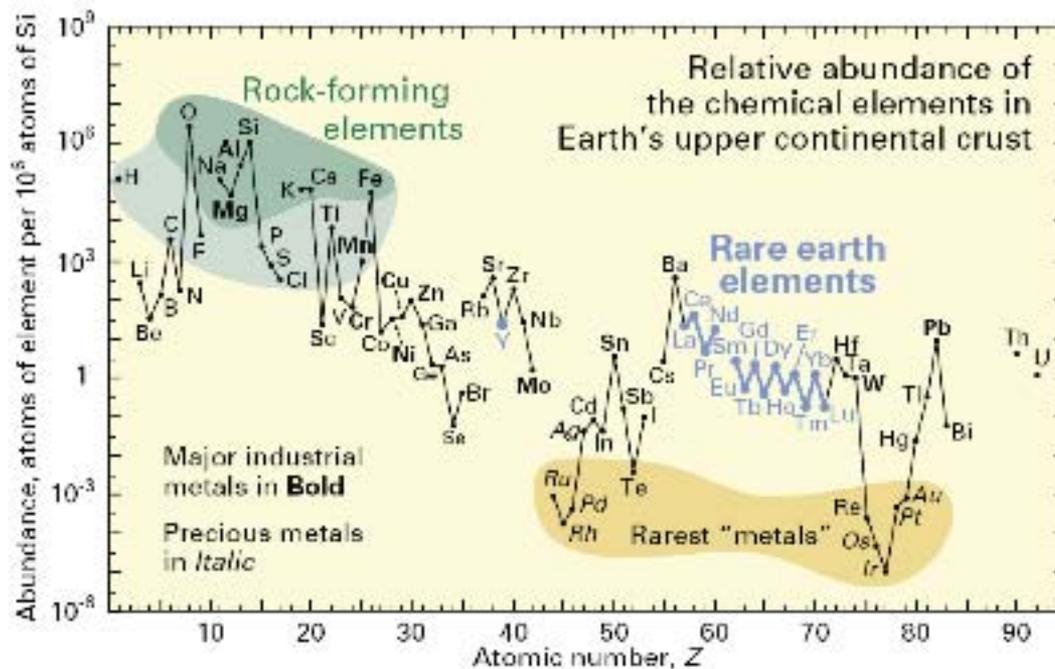


Forest

©1994 Encyclopaedia Britannica, Inc.

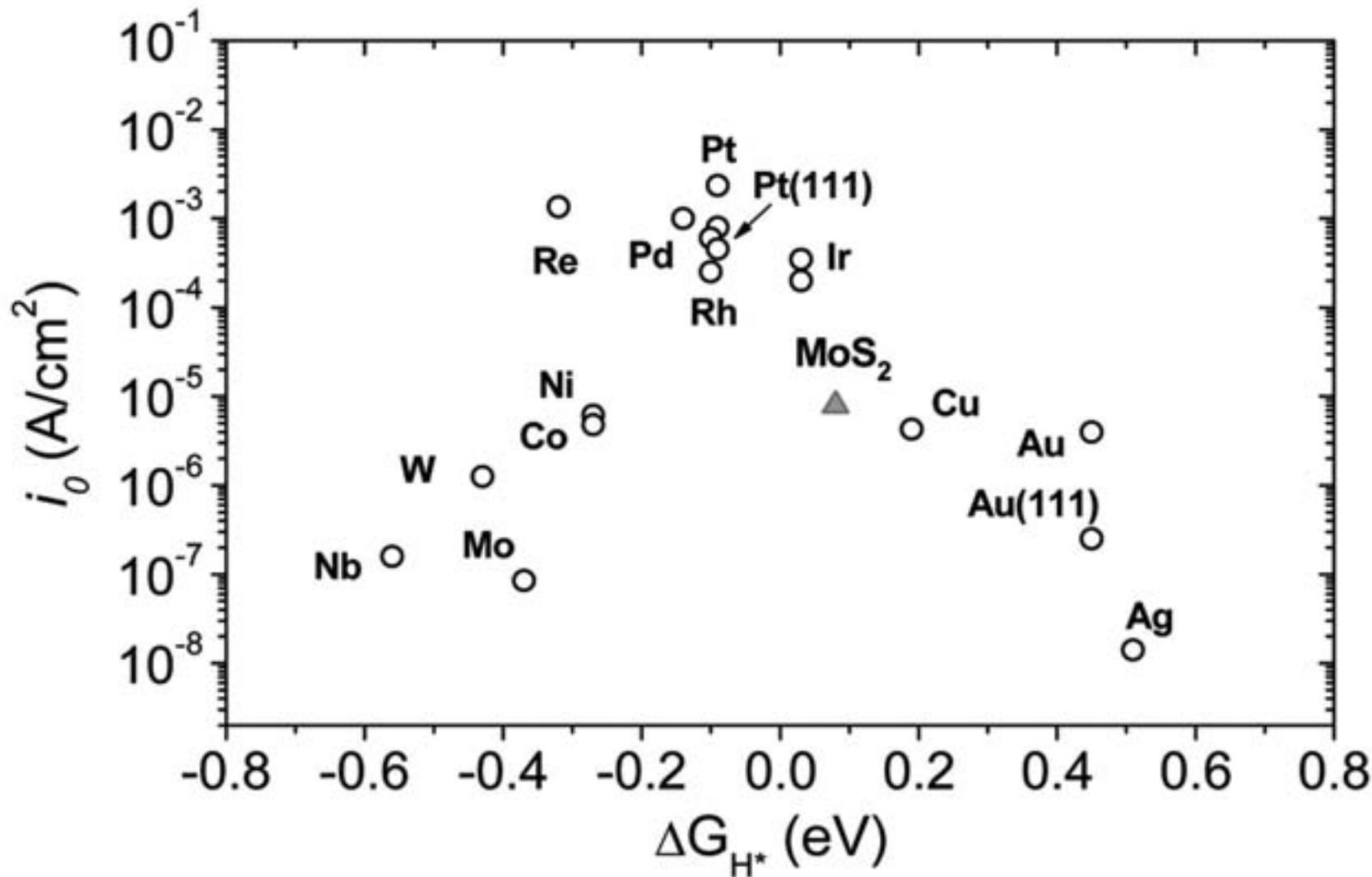
Enables New Materials

- High efficiencies possible despite low diffusion lengths
=> Inexpensive materials
 - **Cheaper traditional materials**
 - Silicon as a model system
 - **Non-traditional, earth-abundant materials**
 - Tandem partners with silicon



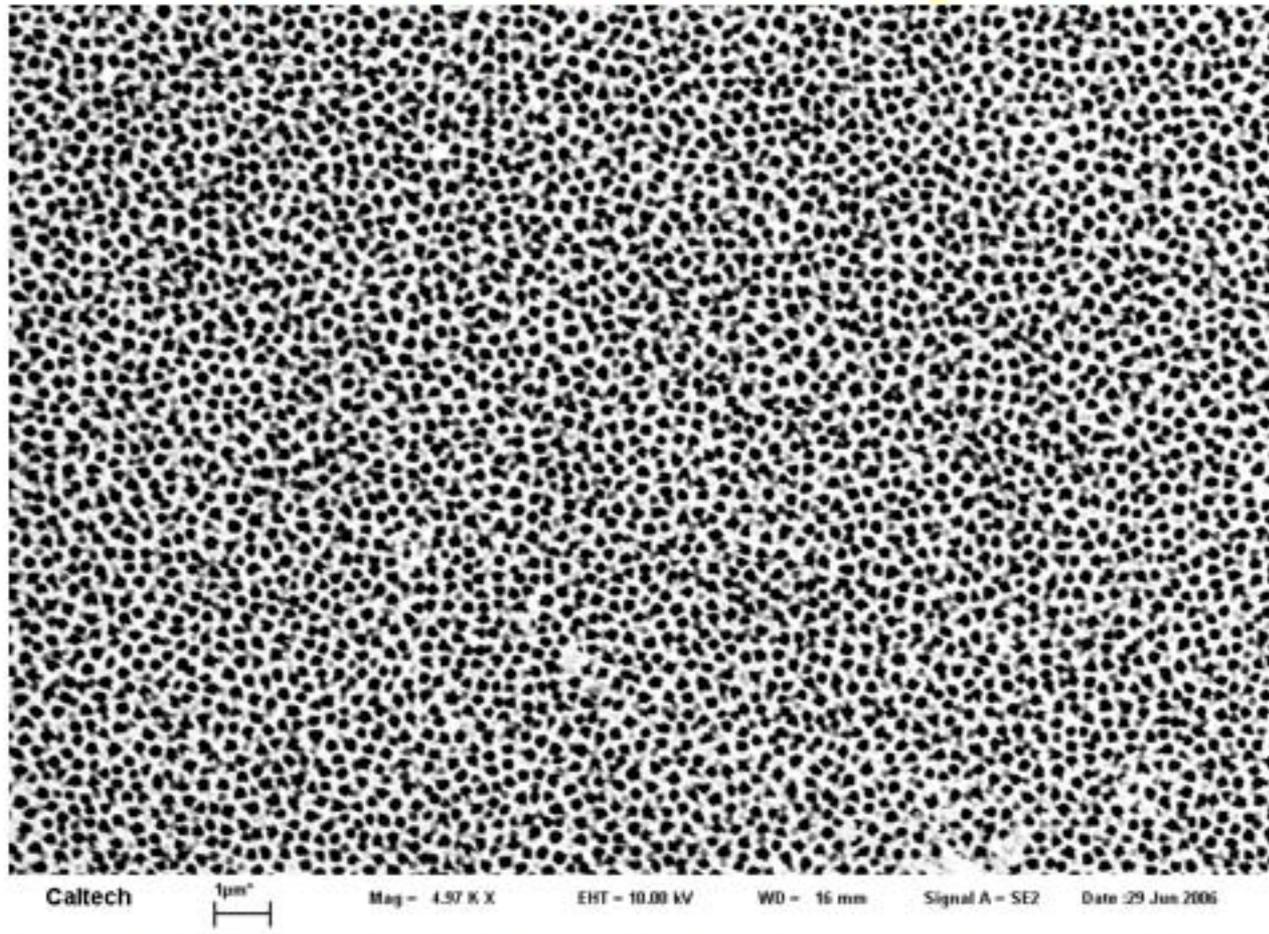


Hydrogen Evolution Reaction





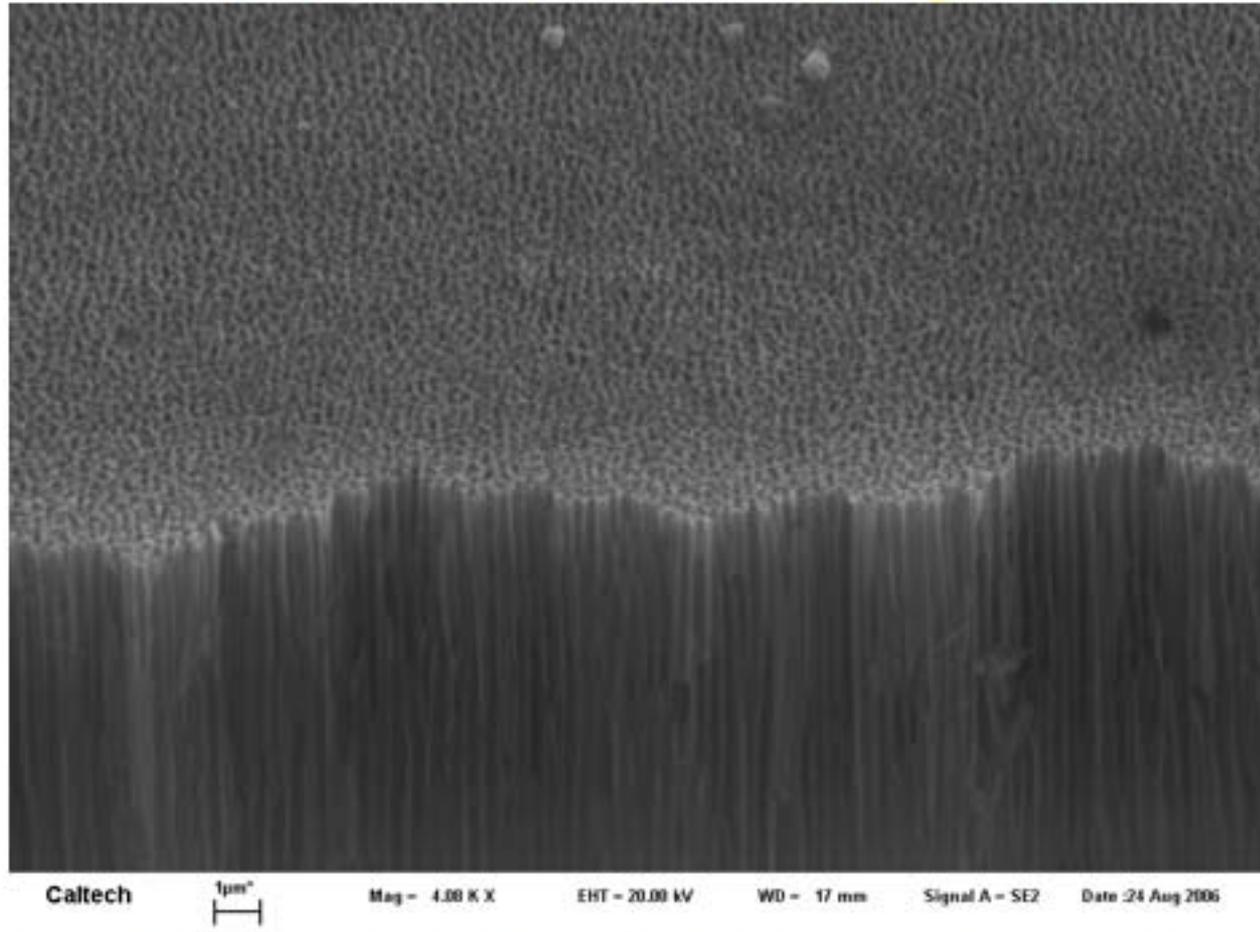
The Alumina Template



- Allows for dense, uniform array of rods
- Carefully controlled dimensions
- Easily removable template



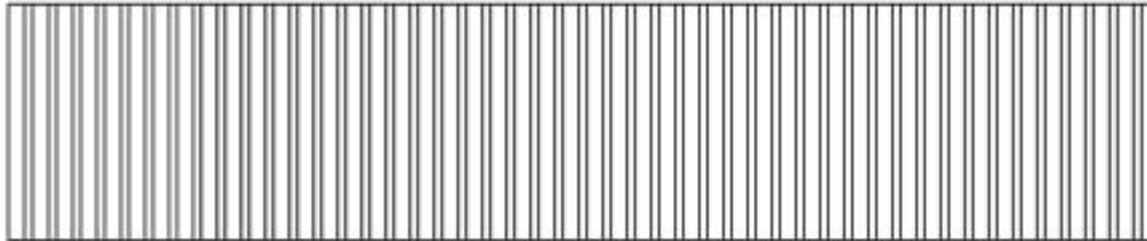
The Alumina Template



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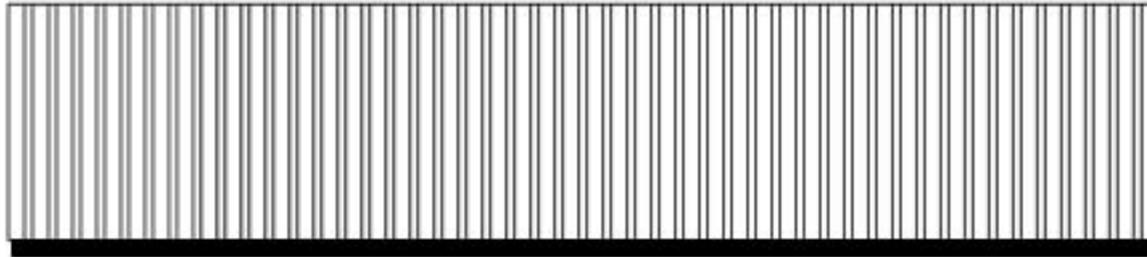
CdSeTe Nanorods



Porous Alumina



CdSeTe Nanorods

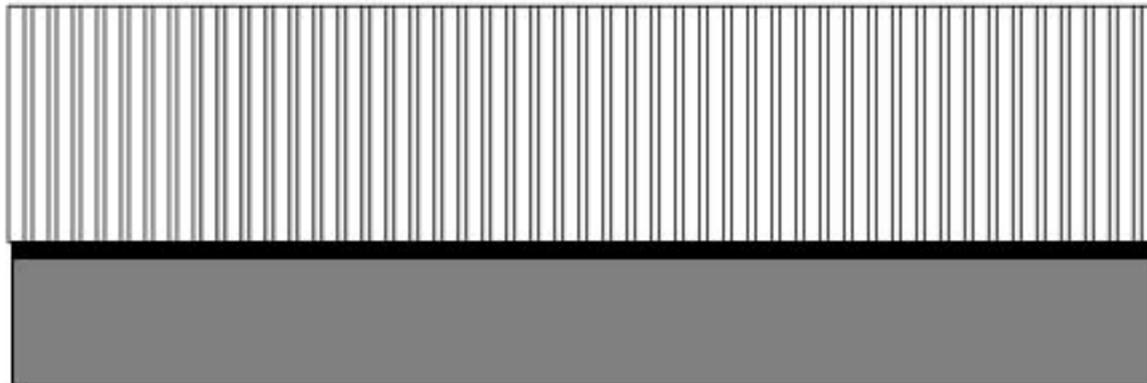


Porous Alumina

CdSe layer to prevent shunting (via sputtering)



CdSeTe Nanorods



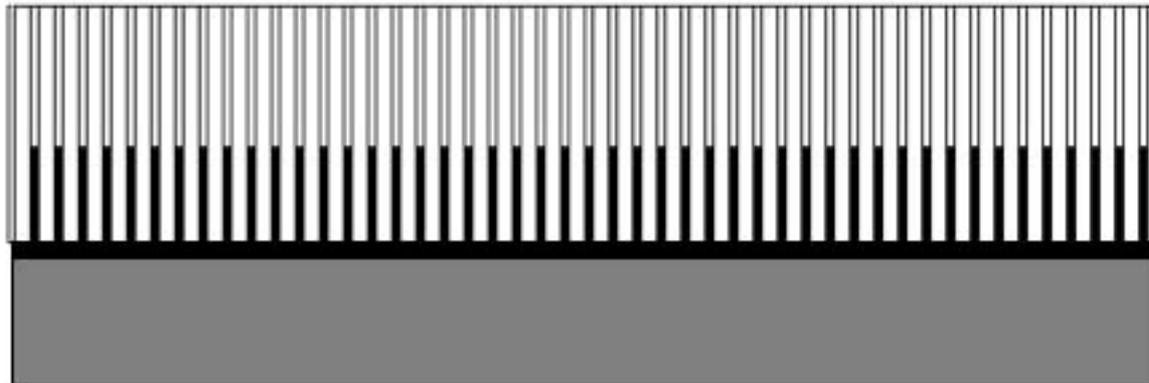
Porous Alumina

CdSe layer to prevent shunting (via sputtering)

Titanium Back Contact (via sputtering)



CdSeTe Nanorods



Porous Alumina

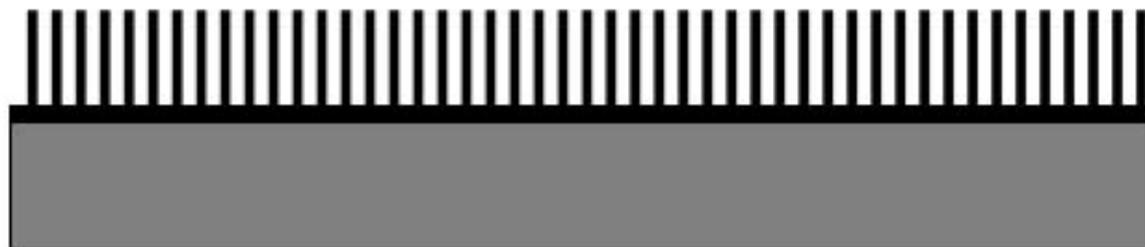
CdSeTe Nanorods
(via electrodeposition)

CdSe layer to
prevent
shunting (via
sputtering)

Titanium Back
Contact
(via sputtering)



CdSeTe Nanorods



Alumina template removed in 1 M NaOH

Porous Alumina

CdSeTe Nanorods
(via electrodeposition)

CdSe layer to
prevent
shunting (via
sputtering)

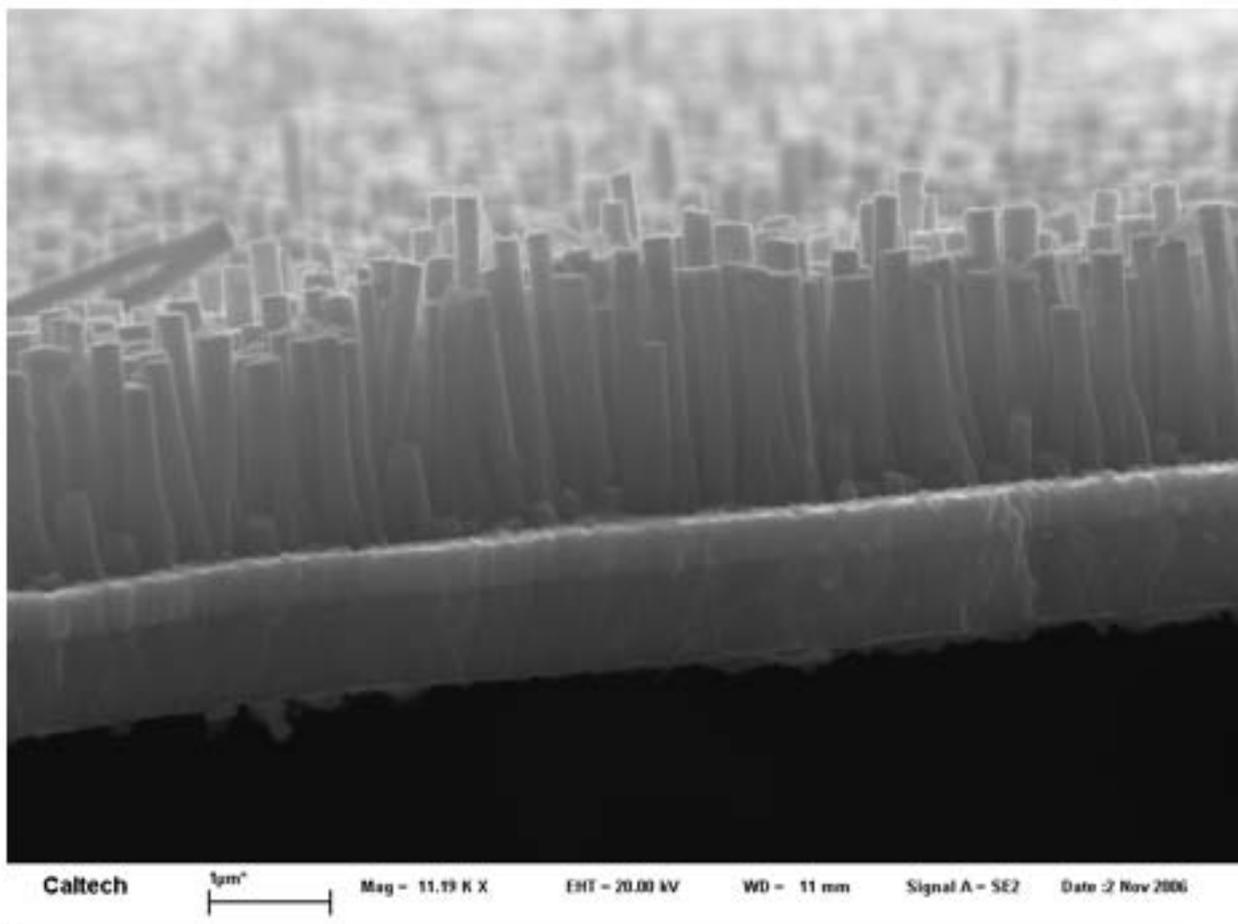
Titanium Back
Contact
(via sputtering)



CdSeTe Nanorods



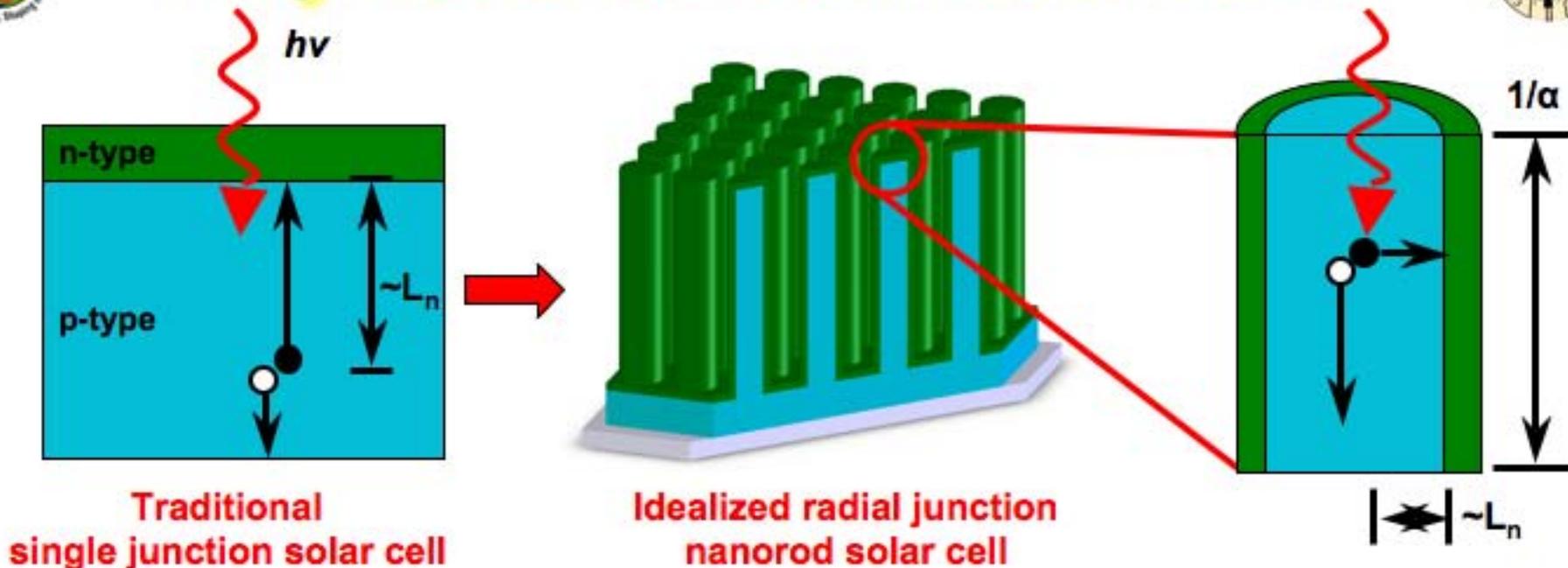
- Use a liquid junction to make a photoelectrochemical cell
- Measure current-voltage properties in the dark and light and compare nanorod performance to an analogous planar electrode



- Thin sputtered CdSe layer to prevent shunting through back contact – negligible contribution to performance



Why Radial Junction Solar Cells?



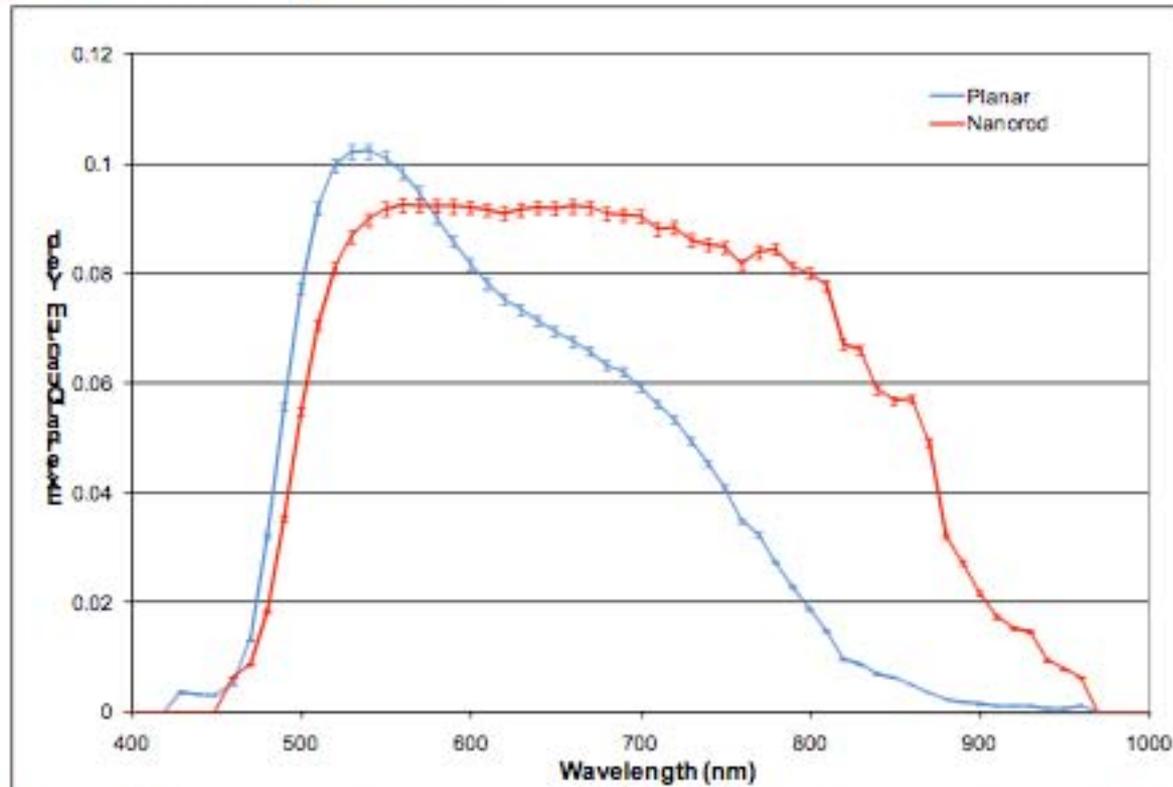
- Traditional device design requires long minority carrier diffusion lengths, and therefore expensive materials
- **Radial geometry allows for high quantum efficiency despite short minority carrier diffusion lengths**



CdSeTe Nanorods



- Spectral response:



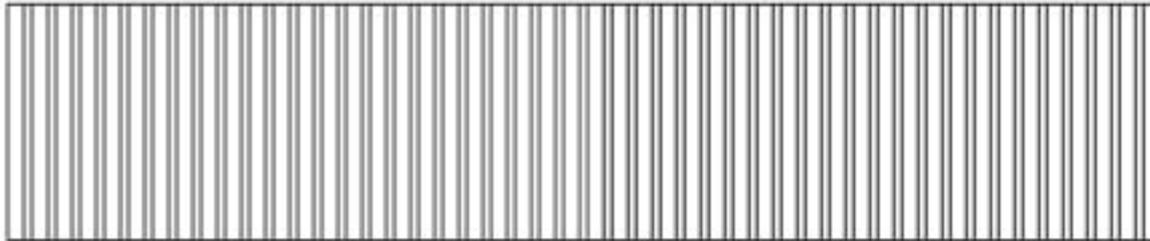
- As expected from IV curves, planar usually exhibits better quantum yields – the above curves were chosen because their similar magnitudes allow for ease of shape comparison
- Shape of the curve is more significant
 - Nanorod samples lose less **quantum yield in the red**
 - Since longer wavelength light penetrates deeper into the semiconductor, this is an indication that the nanorod geometry is **more effectively collecting the carriers**



Si Nanorods



- Nanorod Array Growth Procedure



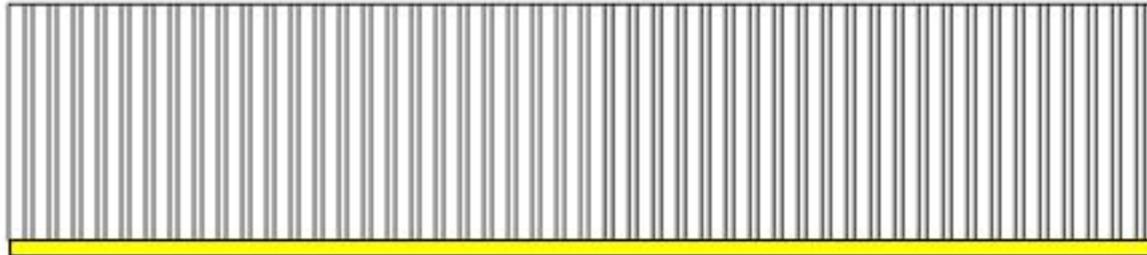
Porous Alumina



Si Nanorods



- Nanorod Array Growth Procedure



Porous Alumina

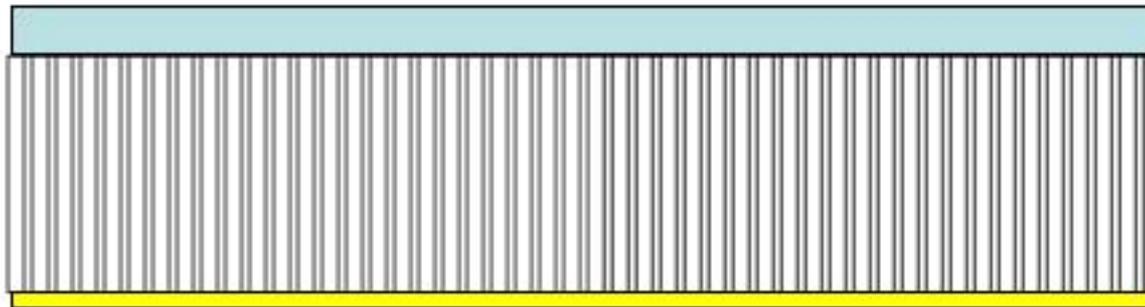
Conductive
Catalyst Metal
(via evaporation)



Si Nanorods



- Nanorod Array Growth Procedure



Mounting Wax
Porous Alumina

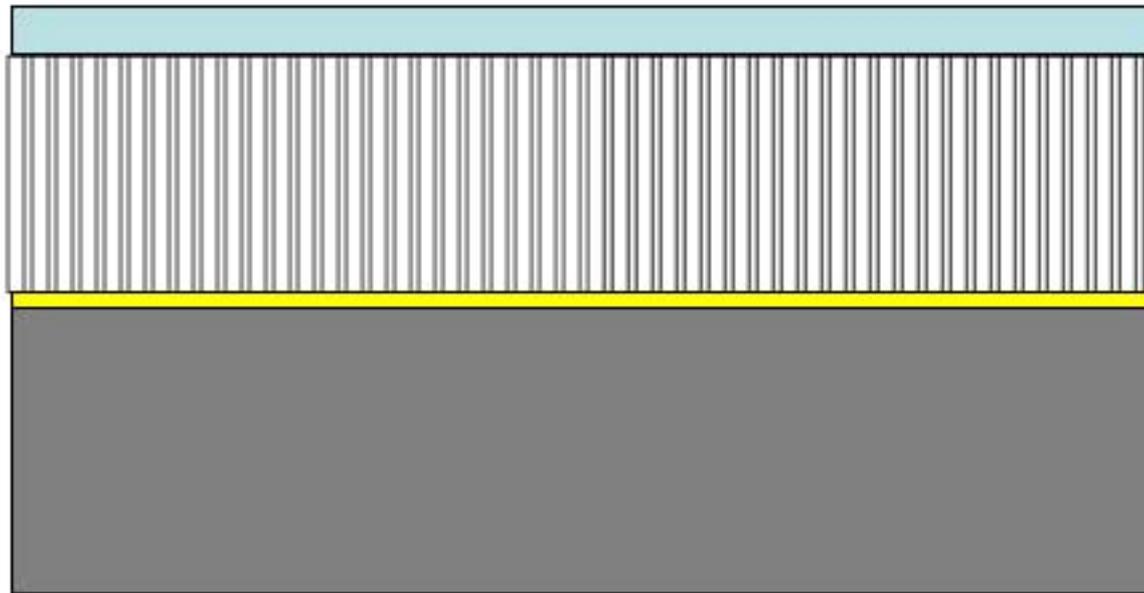
Conductive
Catalyst Metal
(via evaporation)



Si Nanorods



- Nanorod Array Growth Procedure



Mounting Wax
Porous Alumina

Conductive
Catalyst Metal
(via evaporation)

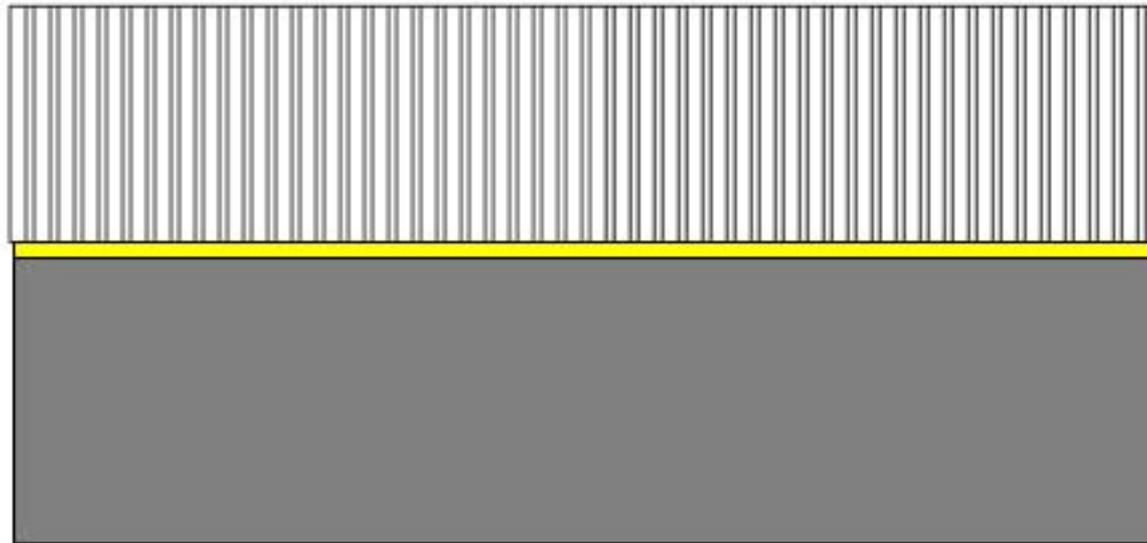
Supportive Nickel
Substrate (via
electrodeposition)



Si Nanorods



- Nanorod Array Growth Procedure



Porous Alumina

Silicon Nanorods

Conductive
Catalyst Metal
(via evaporation)

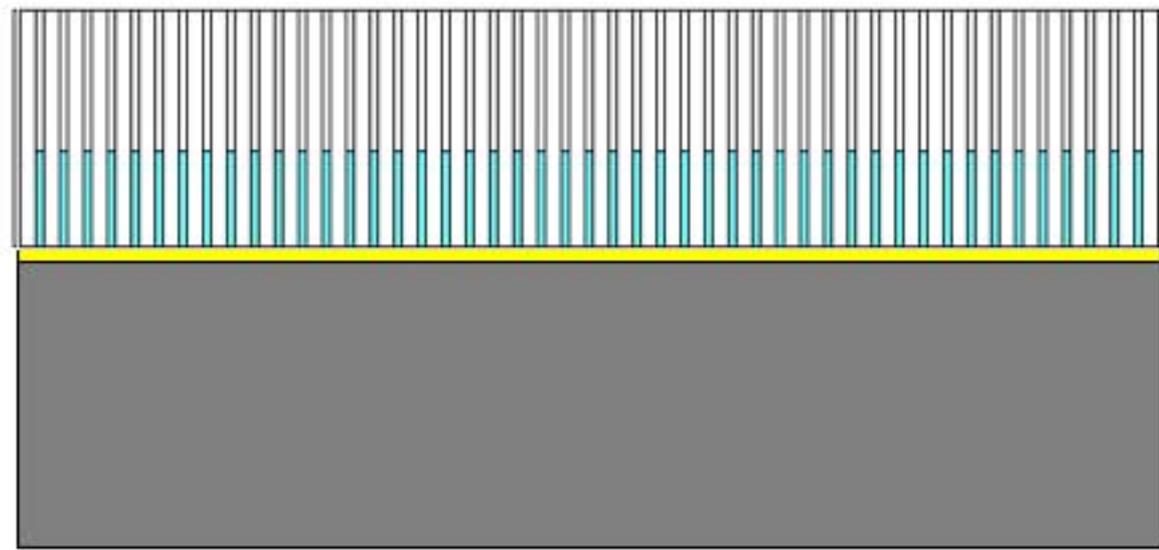
Supportive Nickel
Substrate (via
electrodeposition)



Si Nanorods



- Nanorod Array Growth Procedure



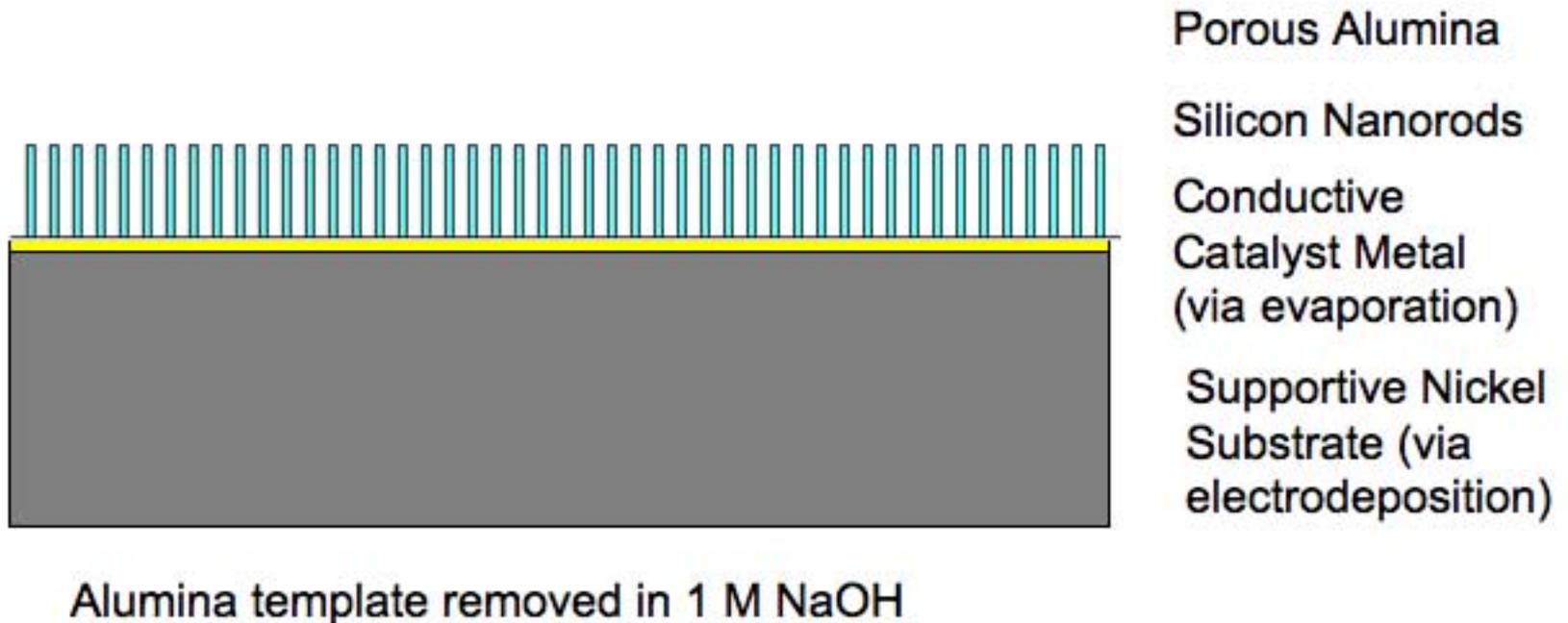
Porous Alumina
Silicon Nanorods
Conductive
Catalyst Metal
(via evaporation)
Supportive Nickel
Substrate (via
electrodeposition)



Si Nanorods



- Nanorod Array Growth Procedure

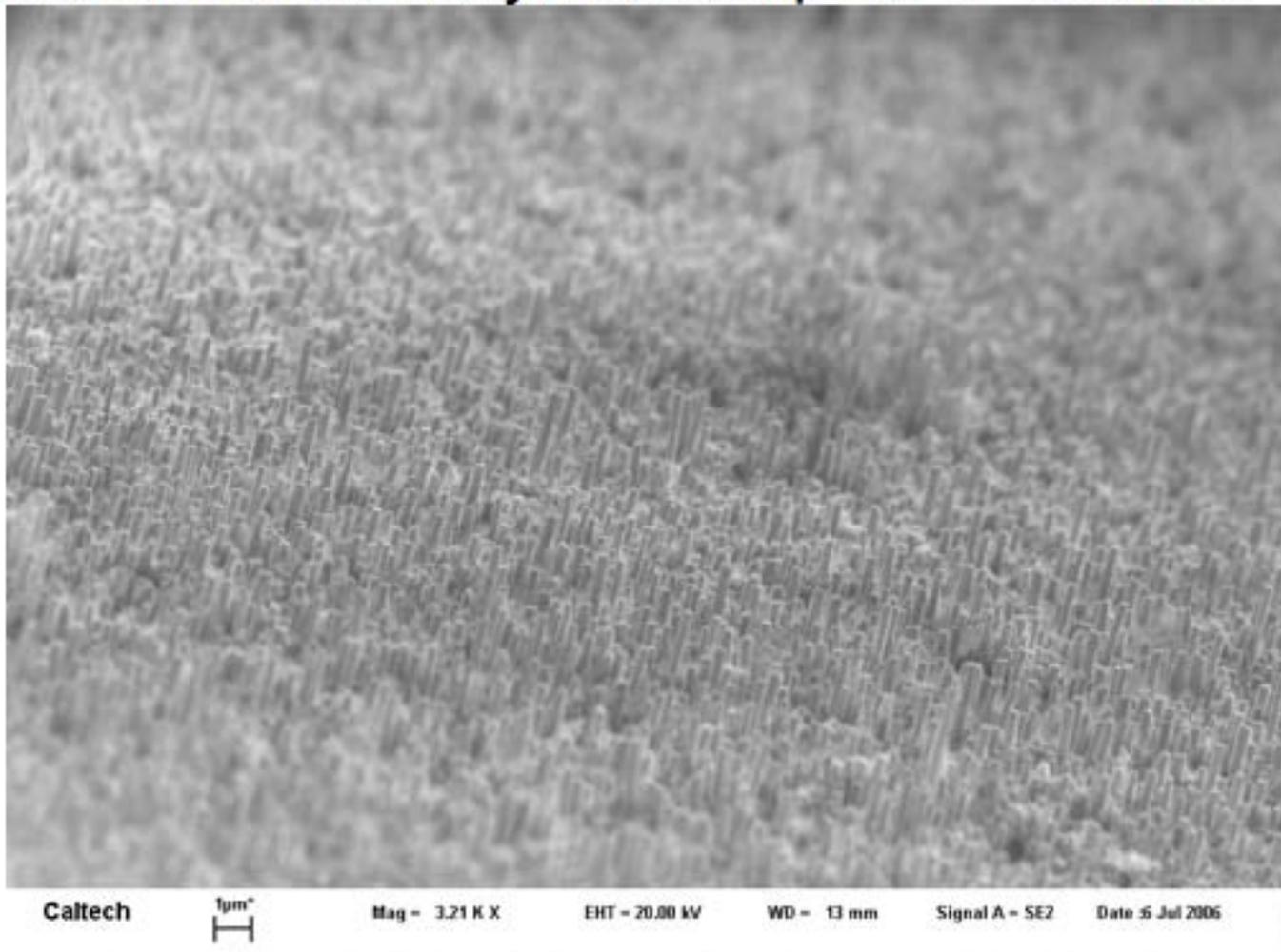


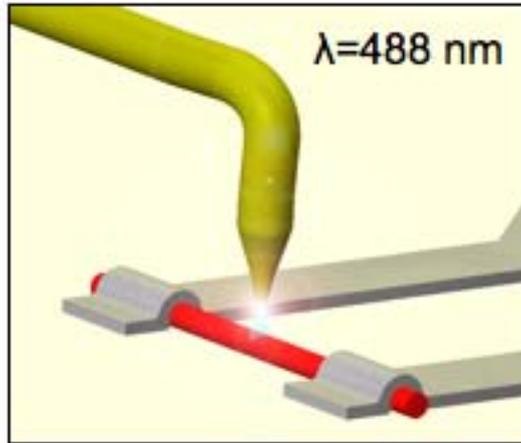


Si Nanorods

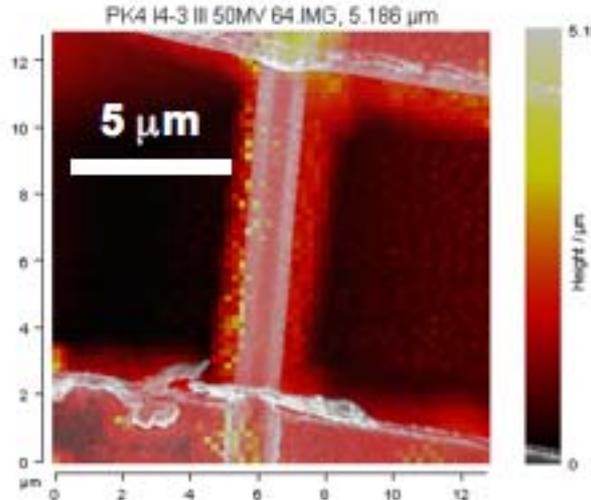


- Silicon nanorod array after template is removed

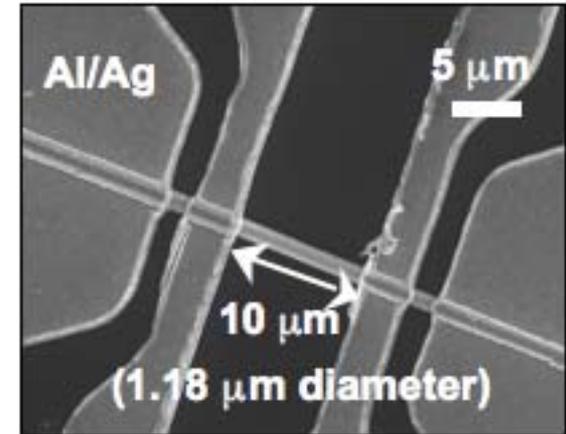




NSOM schematic



SEM-NSOM Topography Overlay



4-Point Probe

- Near-field scanning optical microscopy (NSOM) can measure nanowire photoconductivity as a function of excitation location.
- Carrier collection lengths can be studied as a function of nanowire diameter, growth conditions, passivation, etc...

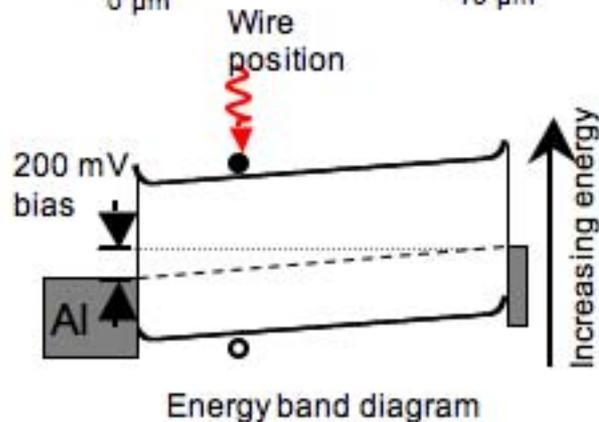
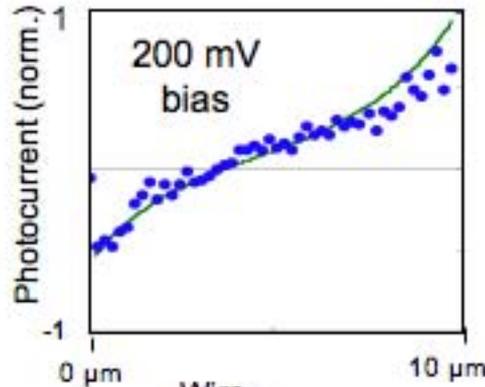
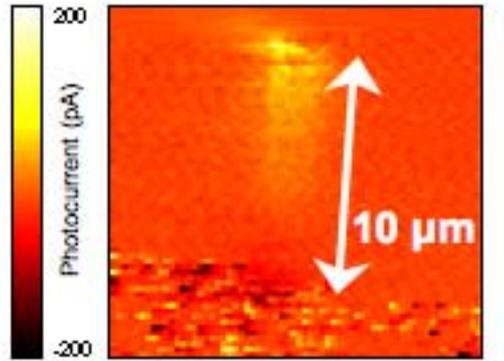


$$R_{\text{wire}} = 17.9 \text{ M}\Omega$$

$$R_{\text{C}} = 200 \text{ k}\Omega$$

$$N_{\text{D}} \sim 5 \times 10^{13} \text{ cm}^{-3}$$

Effective diffusion length



Charge transport by drift and diffusion:

$$J_n(x) = q\mu_n n(x)E(x) + qD_n \frac{\partial \delta n}{\partial x}$$

Charge continuity for electrons with effective, single- τ recombination rate:

$$\frac{\partial \delta n}{\partial t} = \frac{1}{q} \frac{\partial J_n}{\partial x} - \frac{\partial \delta n}{\tau_{n,eff}} + g_n$$

Monitor terminal current as function of injection point:

$$J_{meas} = J_n |_{x=0} + J_p |_{x=0} \quad \text{when} \quad g_{n,p} |_{x=x_{inj}} = I_{ph}$$

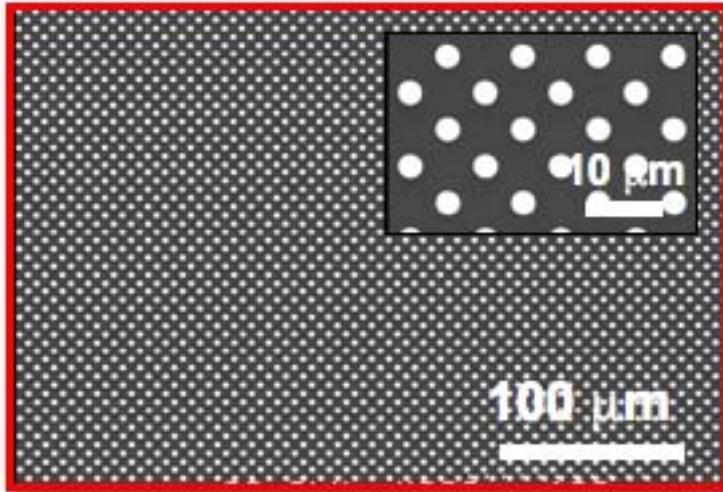
Vary τ to match measured photocurrent profile:

$$L_{n,eff} = \sqrt{D_n \tau_{n,eff}} = 1.9 \mu\text{m} \quad \leftrightarrow \quad \tau_{n,eff} \approx 1 \text{ ns}$$

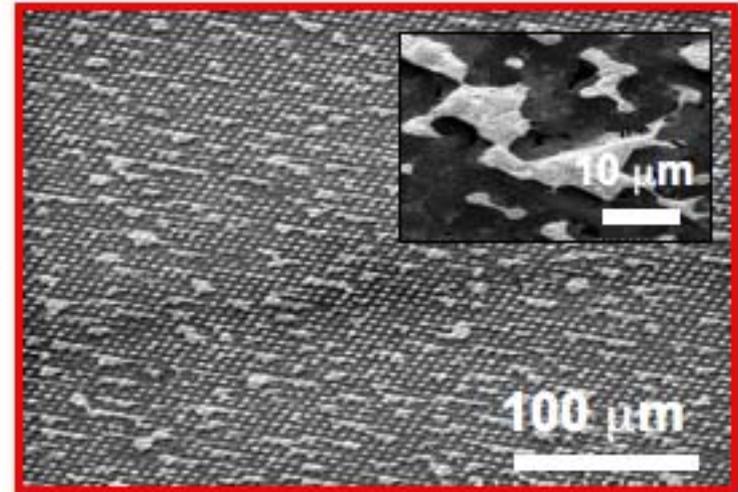
$$L_{p,eff} = \sqrt{D_p \tau_{p,eff}} = 2.2 \mu\text{m} \quad \leftrightarrow \quad \tau_{p,eff} \approx 4 \text{ ns}$$

NSOM suggests minority carrier collection length is comparable to wire diameter.

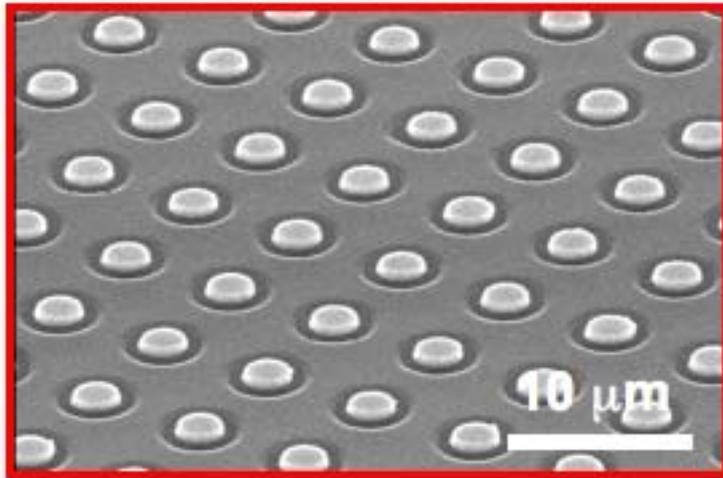
No oxide buffer layer



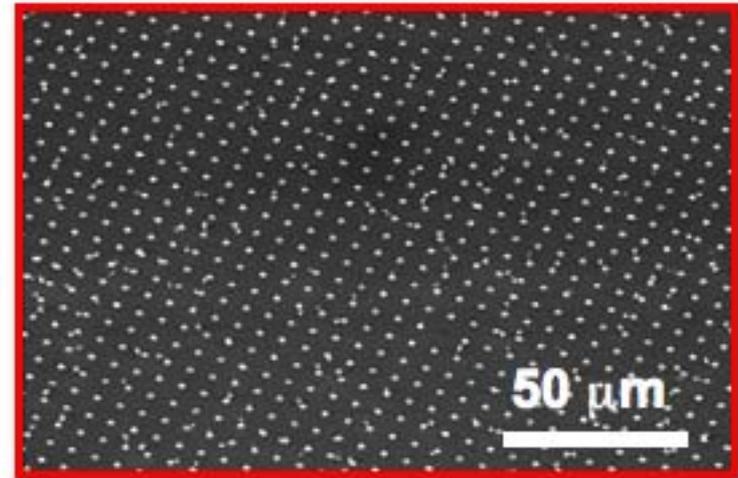

H₂ anneal
1000°C



Oxide buffer layer




H₂ anneal
1000°C

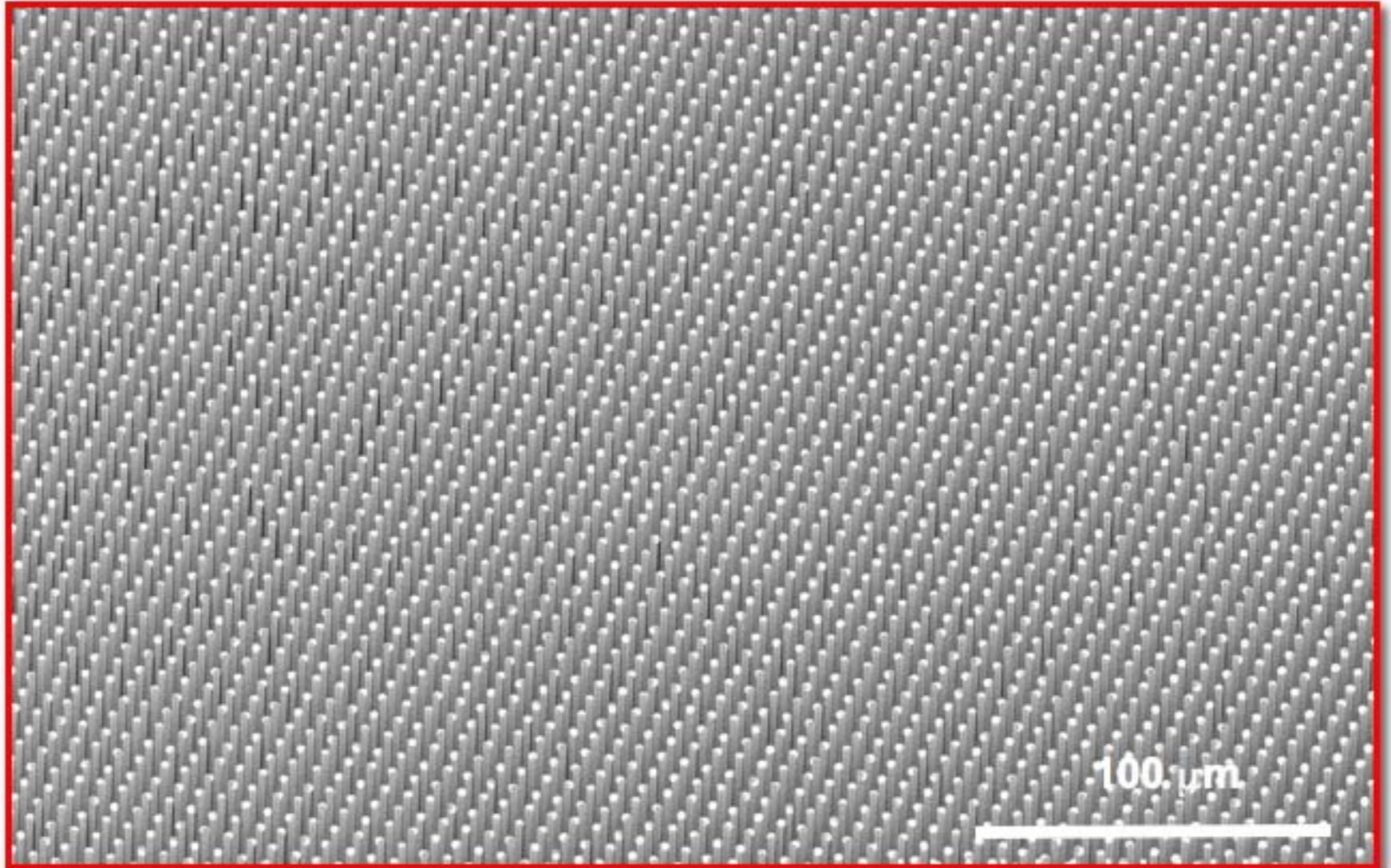


3 μm array, 500 nm Au, $T_{\text{growth}} = 1000^\circ\text{C}$, $P_{\text{growth}} = 760$ Torr

An oxide buffer layer is critical for maintaining pattern fidelity during growth.



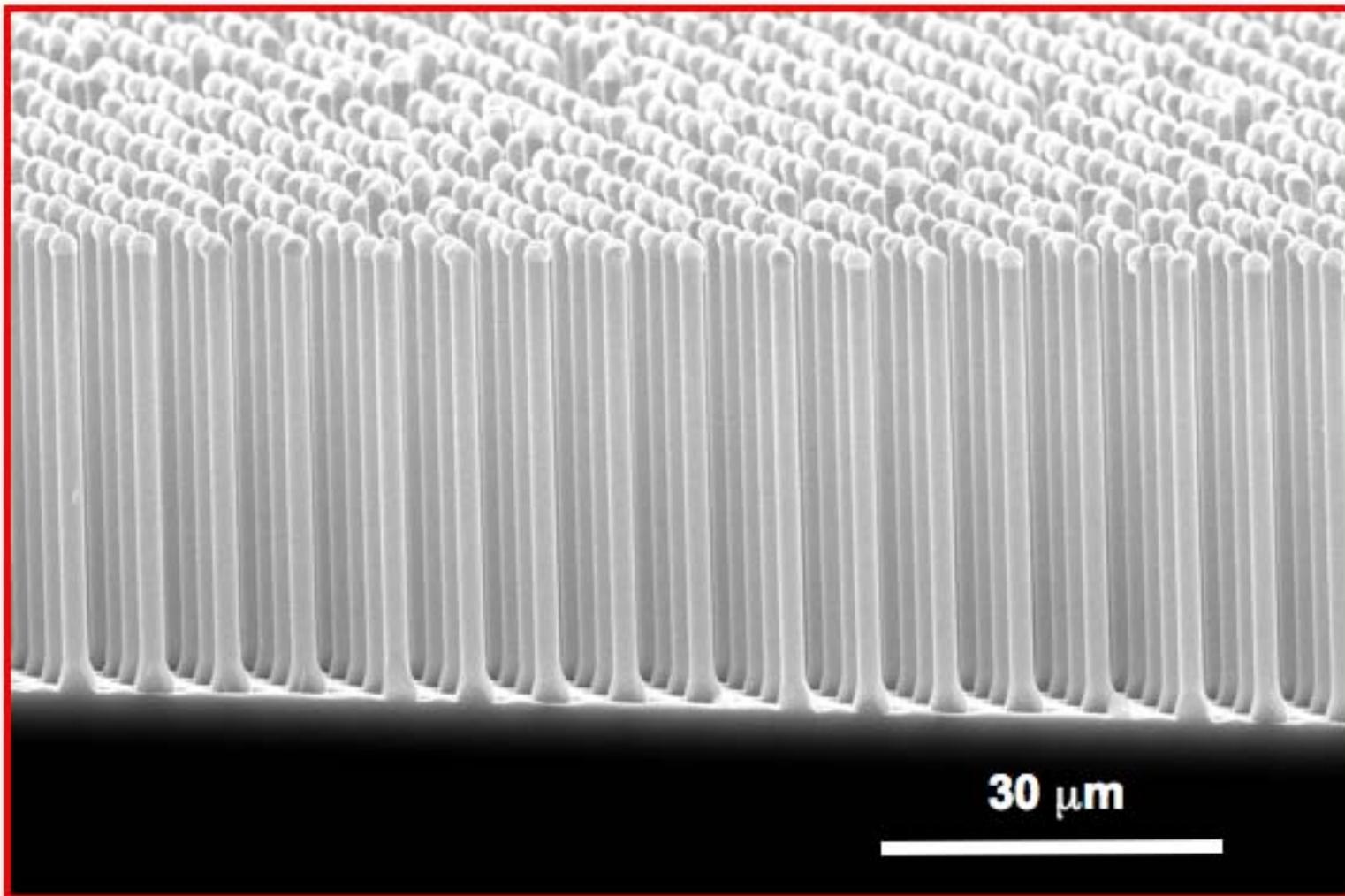
Large Area Au-Catalyzed Si Arrays



3 μm array, 500 nm Au, $T_{\text{growth}} = 1000^{\circ}\text{C}$, $P_{\text{growth}} = 760$ Torr, 30 min growth, 2 mole % SiCl_4 in H_2



Large Area Au-Catalyzed Si Arrays

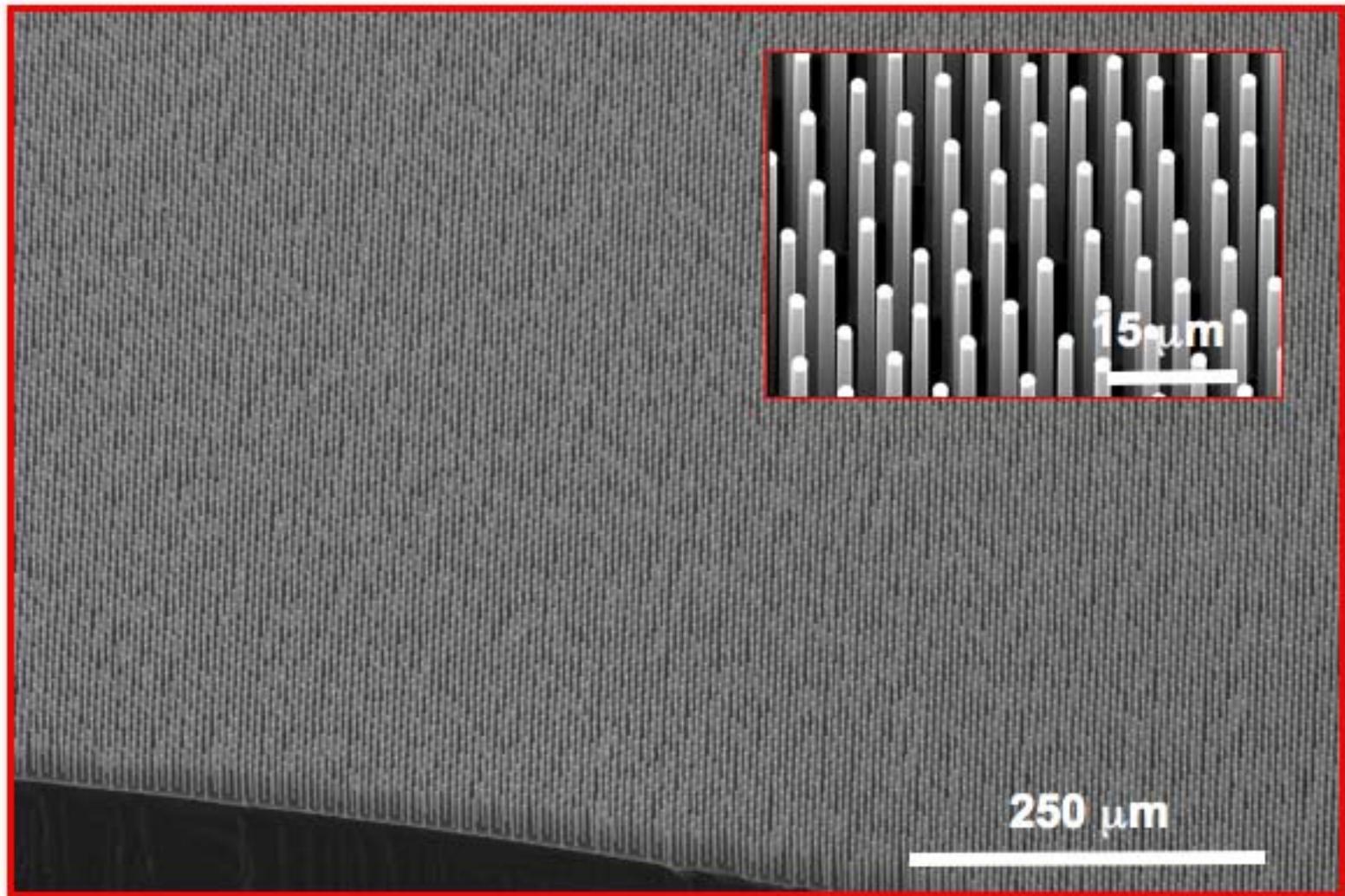


3 μm array, 500 nm Au, $T_{\text{growth}} = 1000^\circ\text{C}$, $P_{\text{growth}} = 760$ Torr, 30 min growth, 2 mole % SiCl_4 in H_2

Nearly 100% vertically aligned, 75 μm length microwire arrays over areas > 1 cm^2 .



Copper-Catalyzed Si Wire Arrays



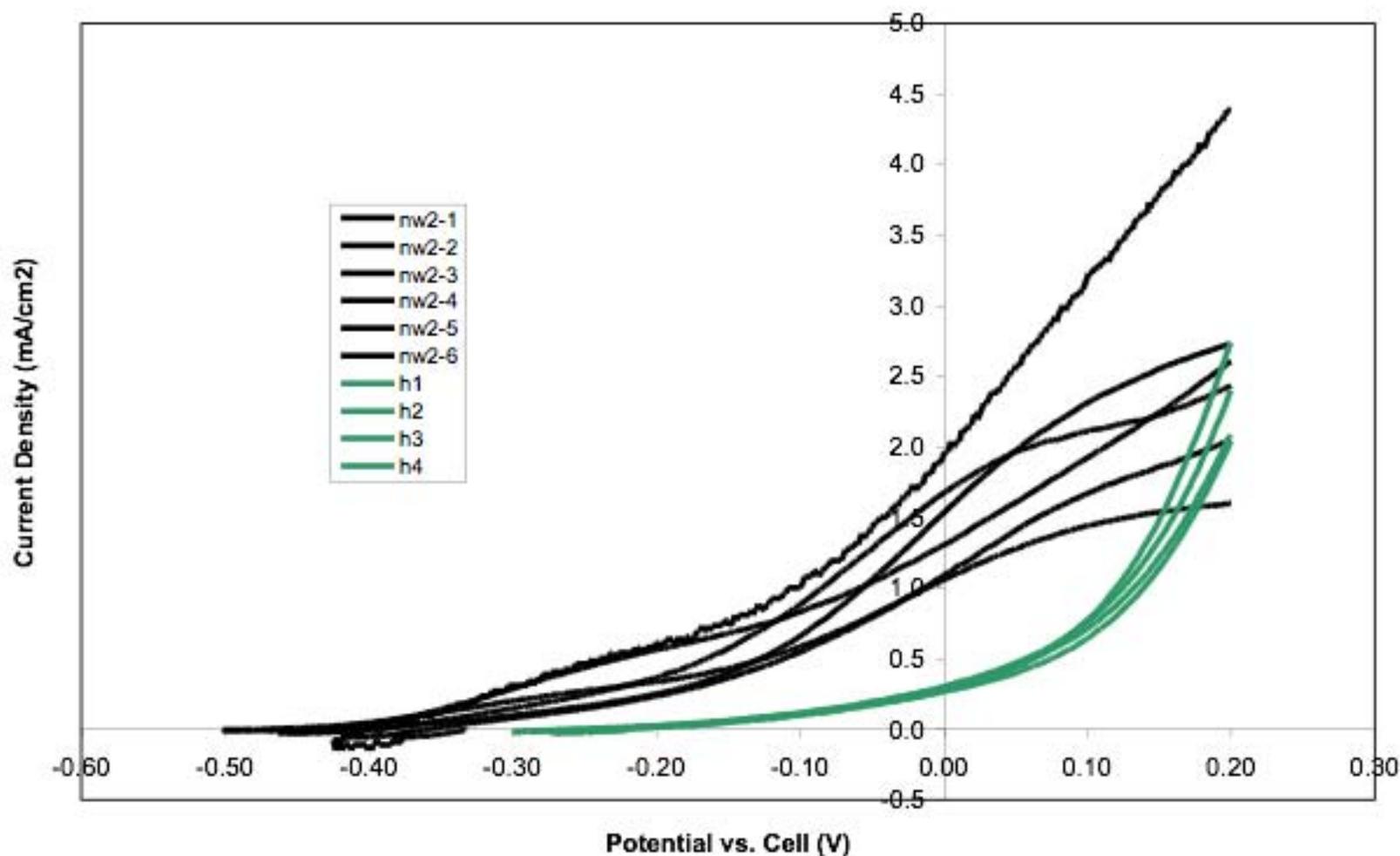
3 μm array, 500 nm Cu, $T_{\text{growth}} = 1000^\circ\text{C}$, $P_{\text{growth}} = 760$ Torr, 10 min growth, 2 mole % SiCl_4 in H_2

Copper produces wire arrays that are structurally equivalent to gold.



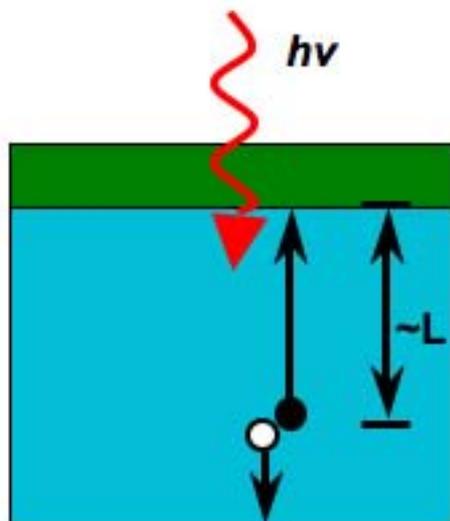
Si Wire Array Junctions

Overlay

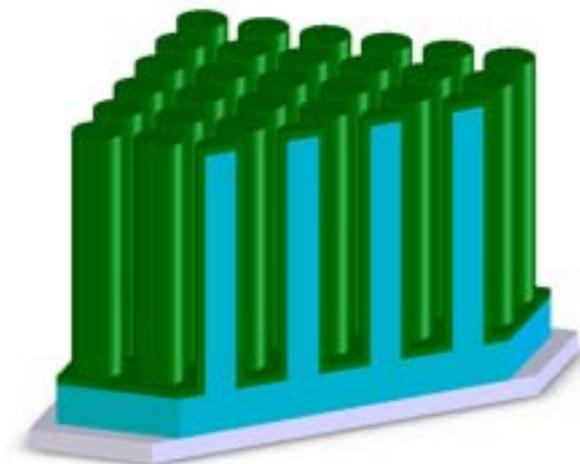




Surface Requirements for Semiconductor Heterojunctions



Traditional planar photovoltaic

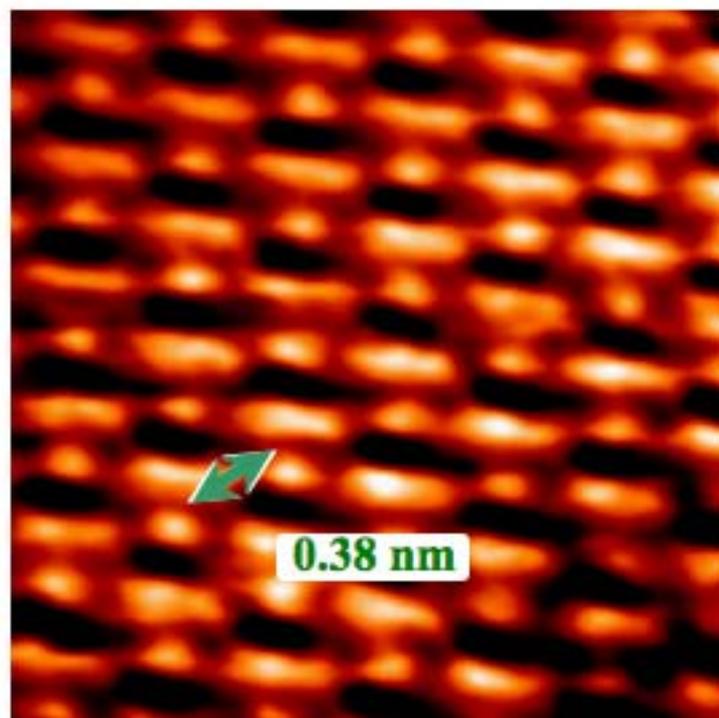
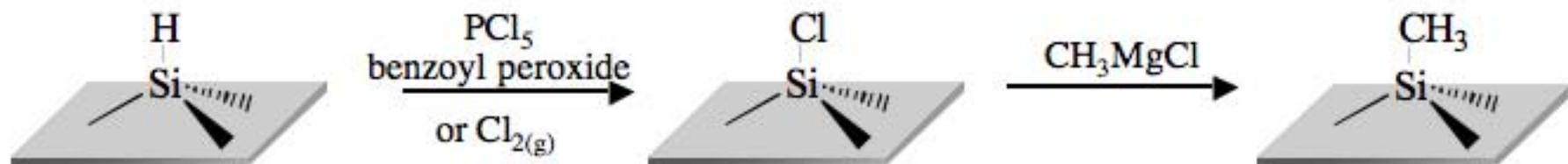


Idealized high aspect ratio photovoltaic

- Low Trap State Density
- Stable in Ambient Conditions
- Facile Interfacial Charge Transfer



Surface Passivation



Measured through
STM, $T = 4 \text{ K}$

1 nm

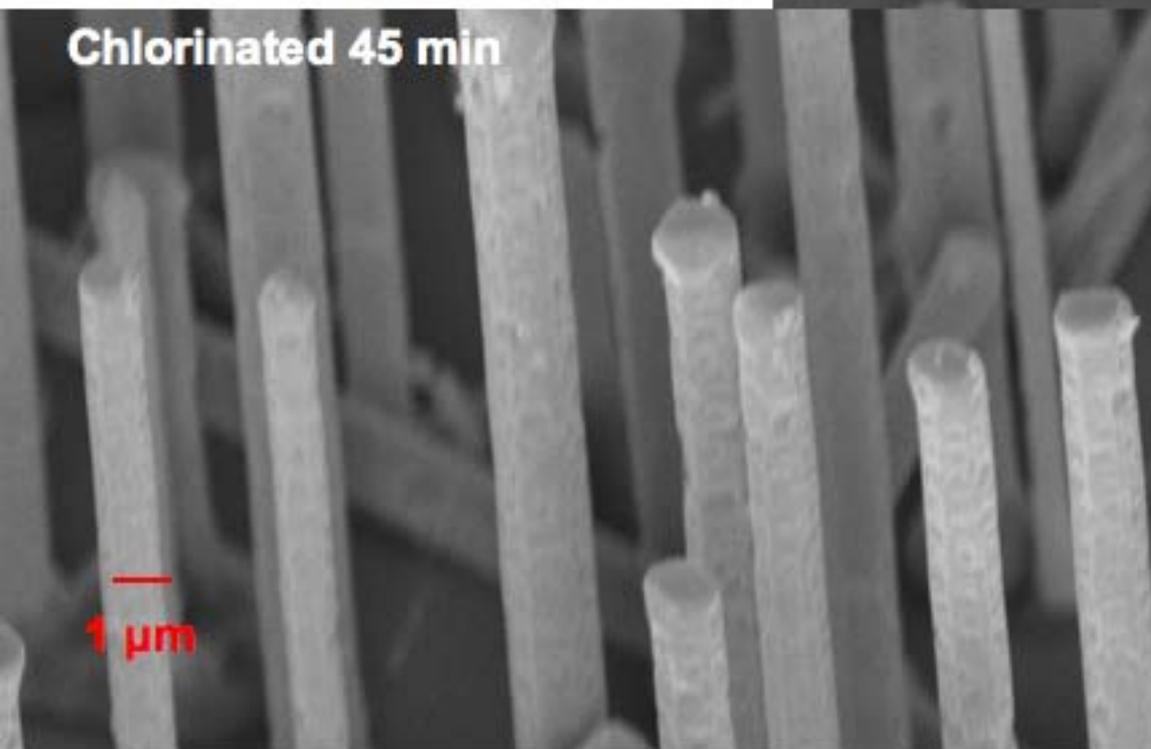
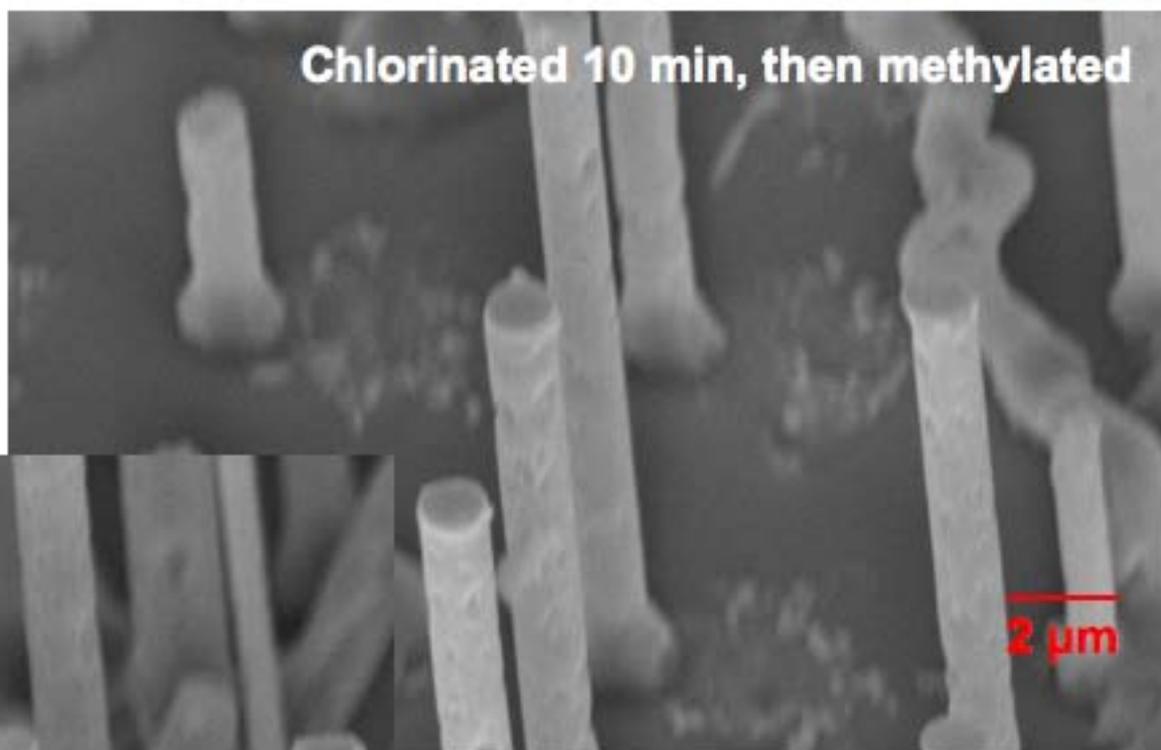
$\text{Si}(111)\text{-CH}_3$



SEM of Chlorinated Si Nanorod Arrays



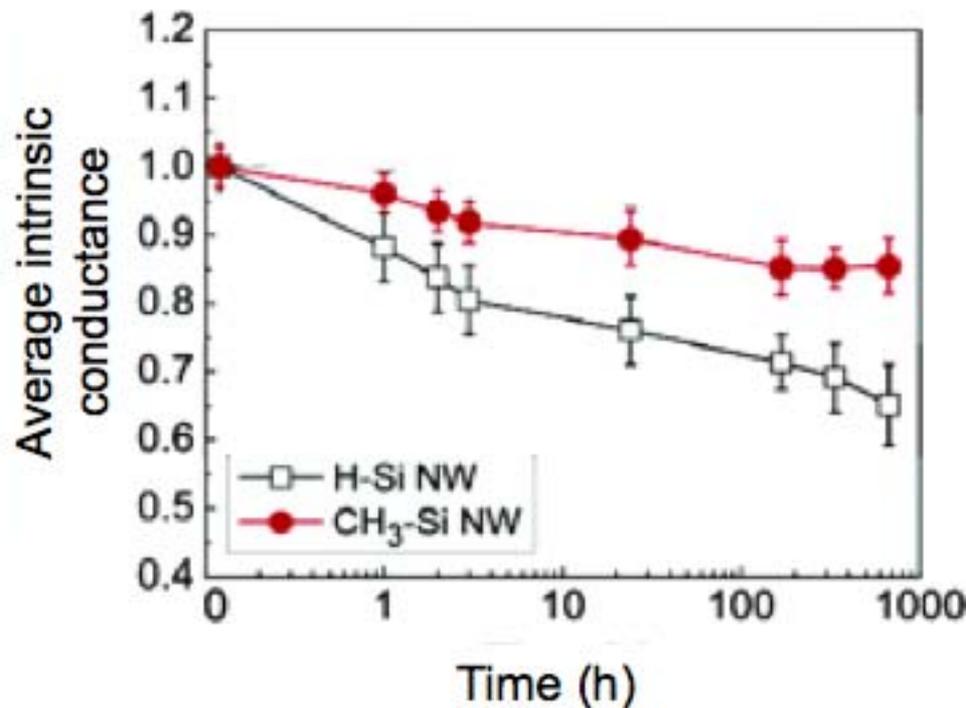
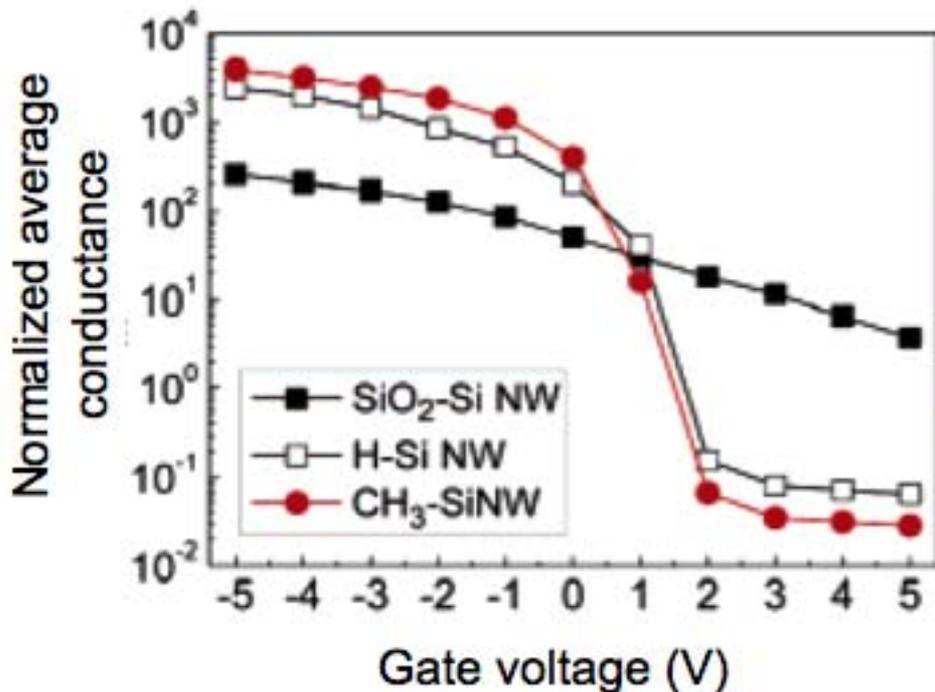
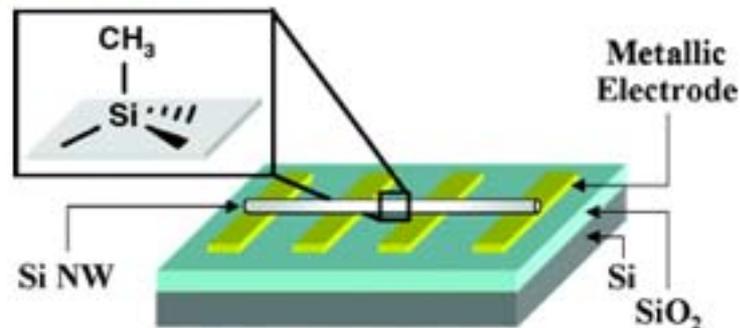
- Chlorination with PCl_5 is known to cause etching of silicon surfaces



- Functionalized surfaces appear rough, but etching is not destructive

Electrical Performance of Methylated Silicon Nanowires

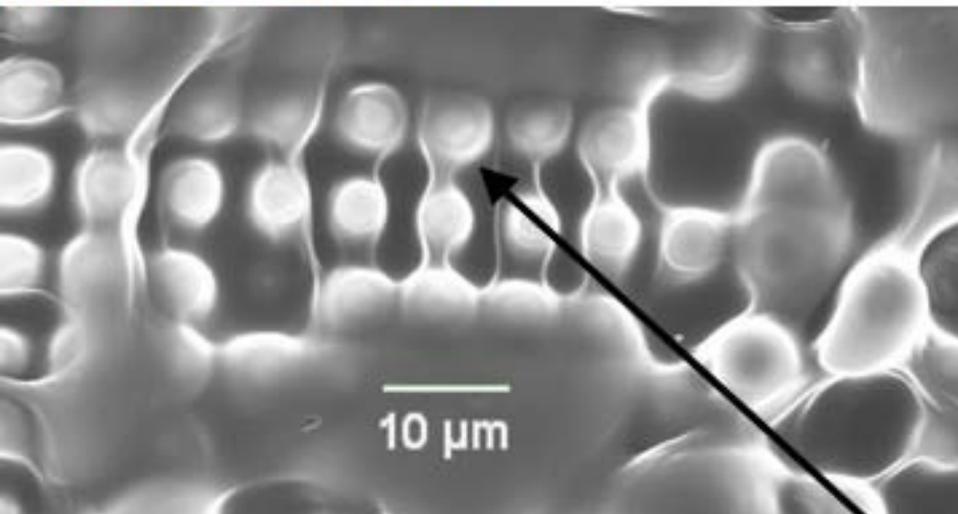
- Methylated wires (60 nm diameter)
 - Sensitive to gate voltage
 - Maintain higher conductance
- Hydrogen terminated surfaces
 - Deteriorate



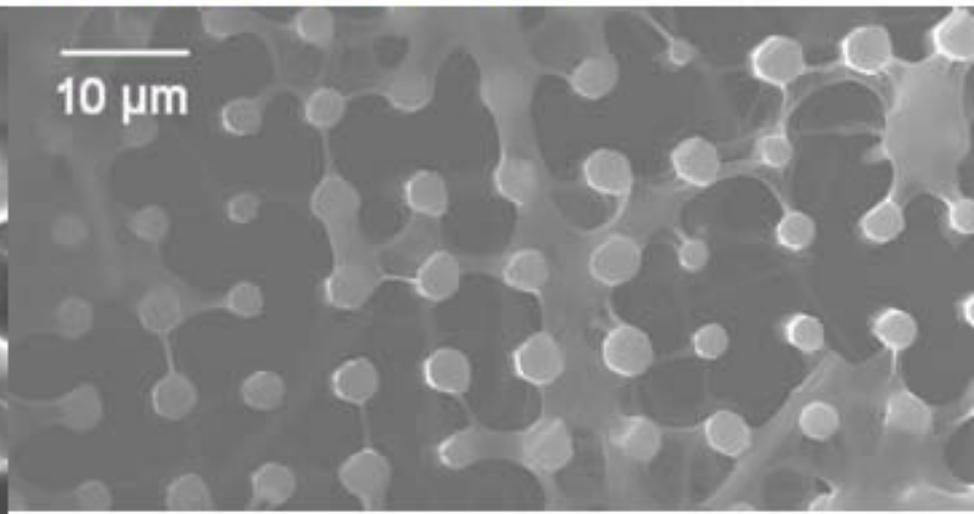
Haick, H.; Hurley, P. T.; Hochbaum, A. I.; Yang, P.; Lewis, N. S. *J. Am. Chem. Soc.* **2006**, *128*, 8990-8991.

Polymerization from Si Rod Surfaces

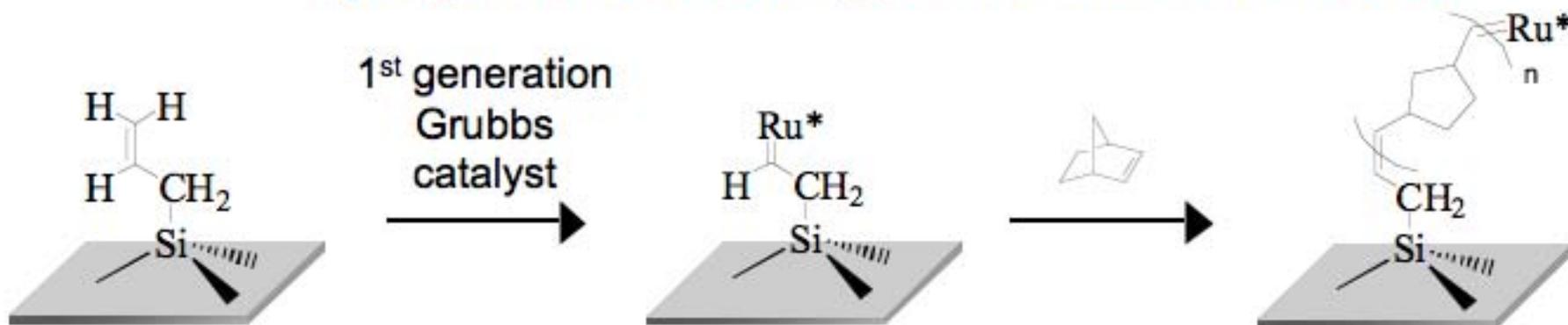
Allylated Si base



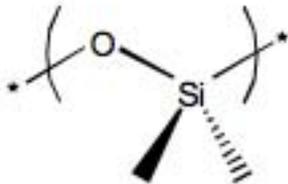
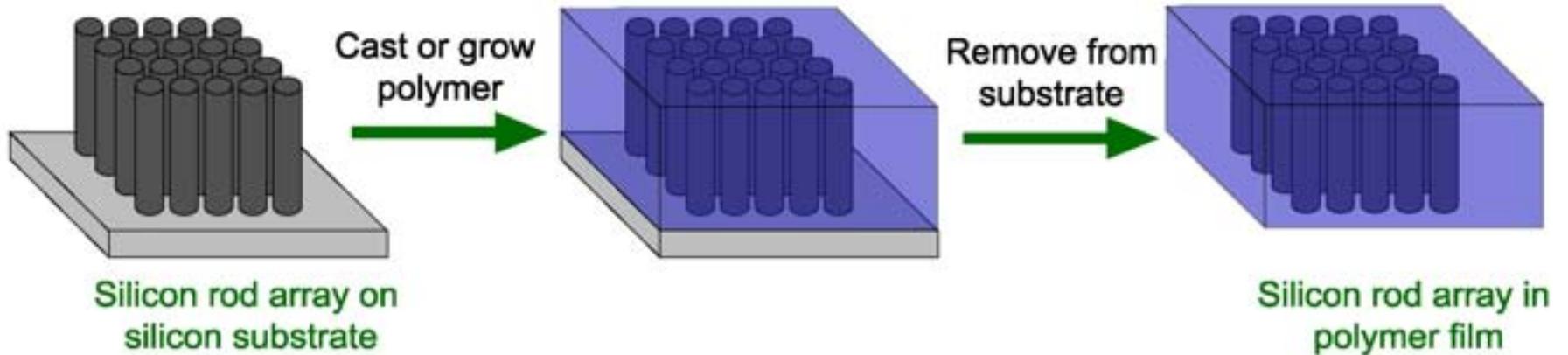
Methylyated Si base



polymer sheath grown around rods!



Polymer Embedding of Si Rod Arrays

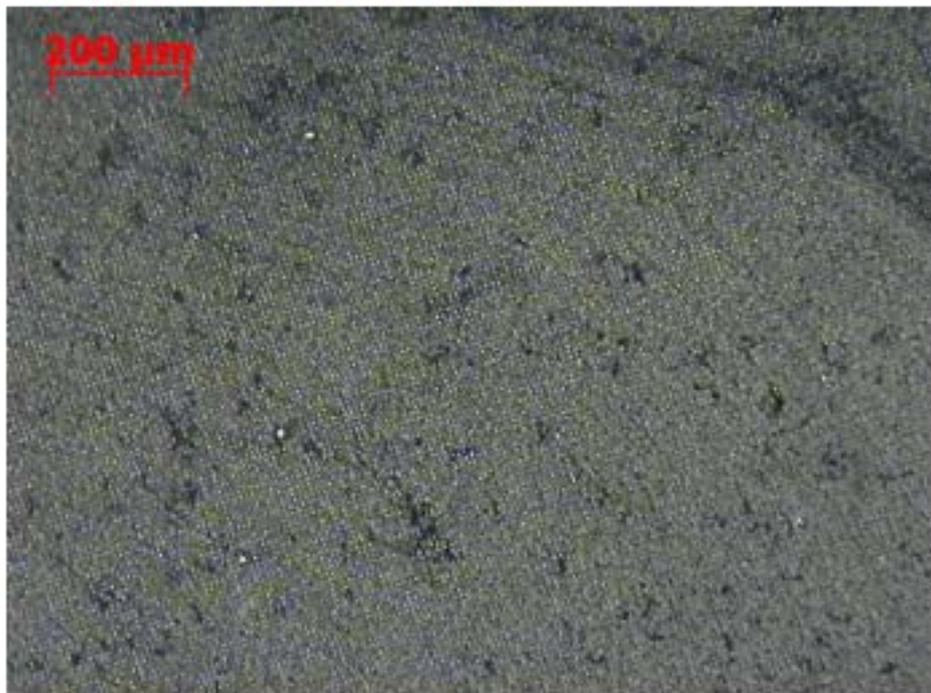


PDMS
(polydimethylsiloxane)



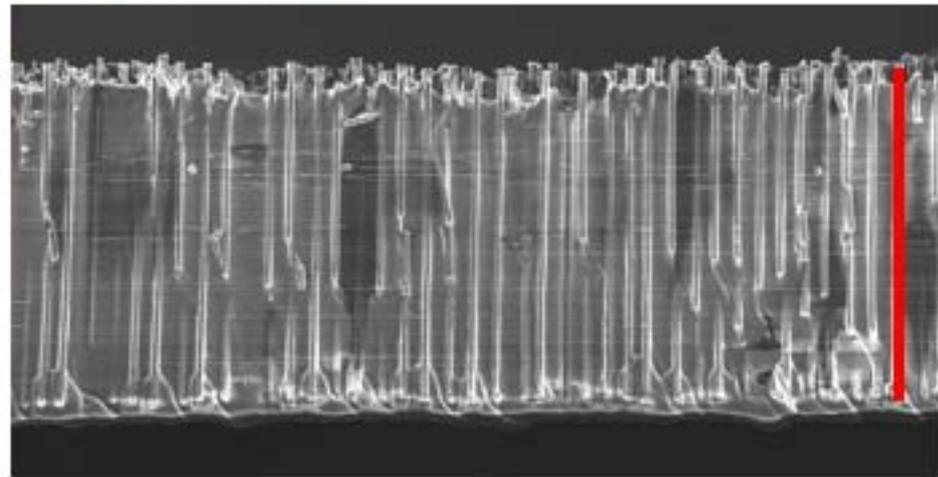
Large Area Rod Array Removal

Top-down view



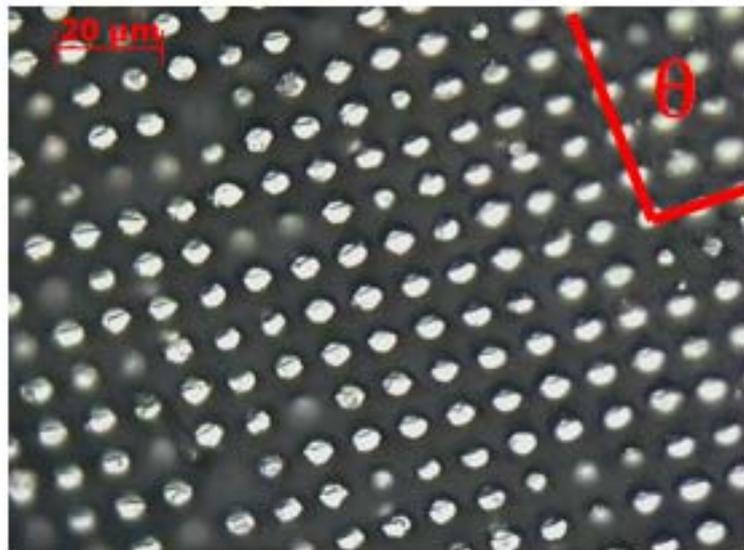
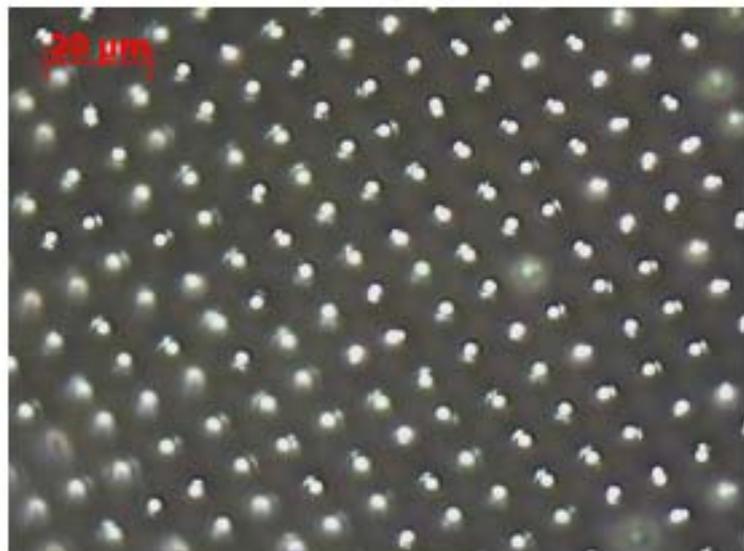
- Large area arrays ($> 1 \text{ cm}^2$) transferred in one piece.

Side view



- Conformal coating from top to bottom of rods

Embedded Rod Pattern Fidelity



- Inter-rod angle and spacing is constant before and after PDMS casting and removal
- Apparent rod diameter differences due to examination of rod tips versus base

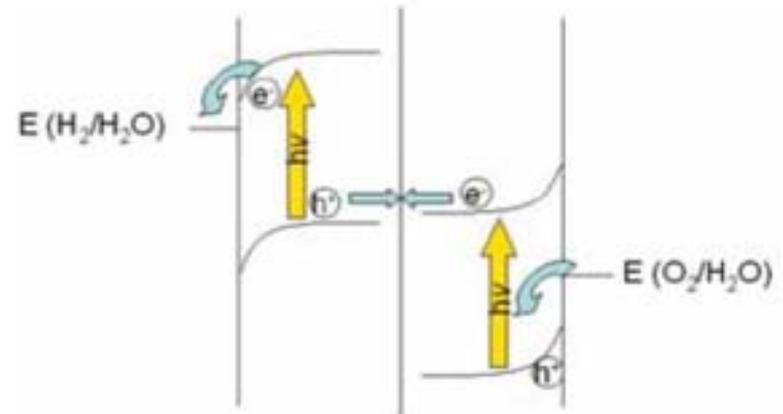
	Rod diameter (μm)	Shortest inter-rod distance (μm)	Angle (θ, °)
Before removal	2.5 ± 2	8.6 ± 2	92 ± 9
After removal	4.6 ± 4	8.8 ± 3	94 ± 2



Dual Junction Nanorod Arrays



- 1.23 V needed to electrolyze water
- Requires a heterojunction or dual junction
- Single absorber: band gap of 2.0-2.6 eV that straddles the necessary potentials
- Photoanode and photocathode absorbers:



Band gaps can better match the solar spectrum (1.1-1.4 eV)

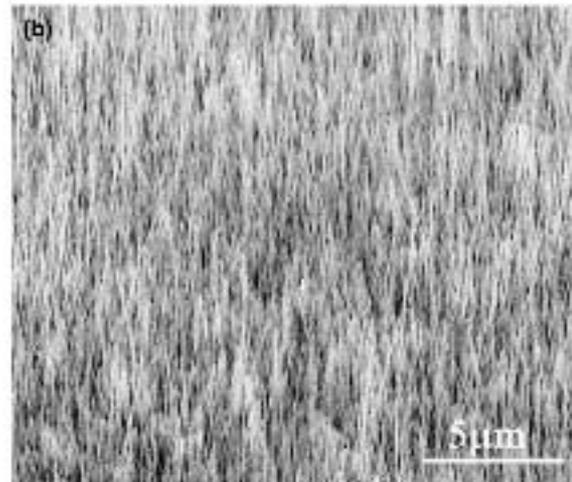
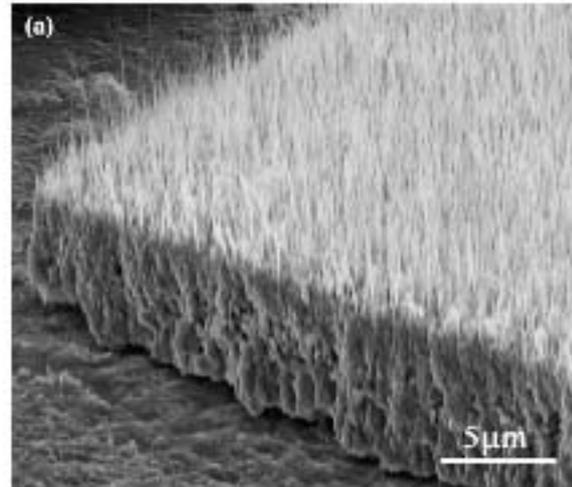
Allows for greater flexibility in materials design

Efficiency could approach 25%

- Optimal structure would have several light-absorbing layers absorbing different portions of the spectrum with an overall potential greater than 1.23 V

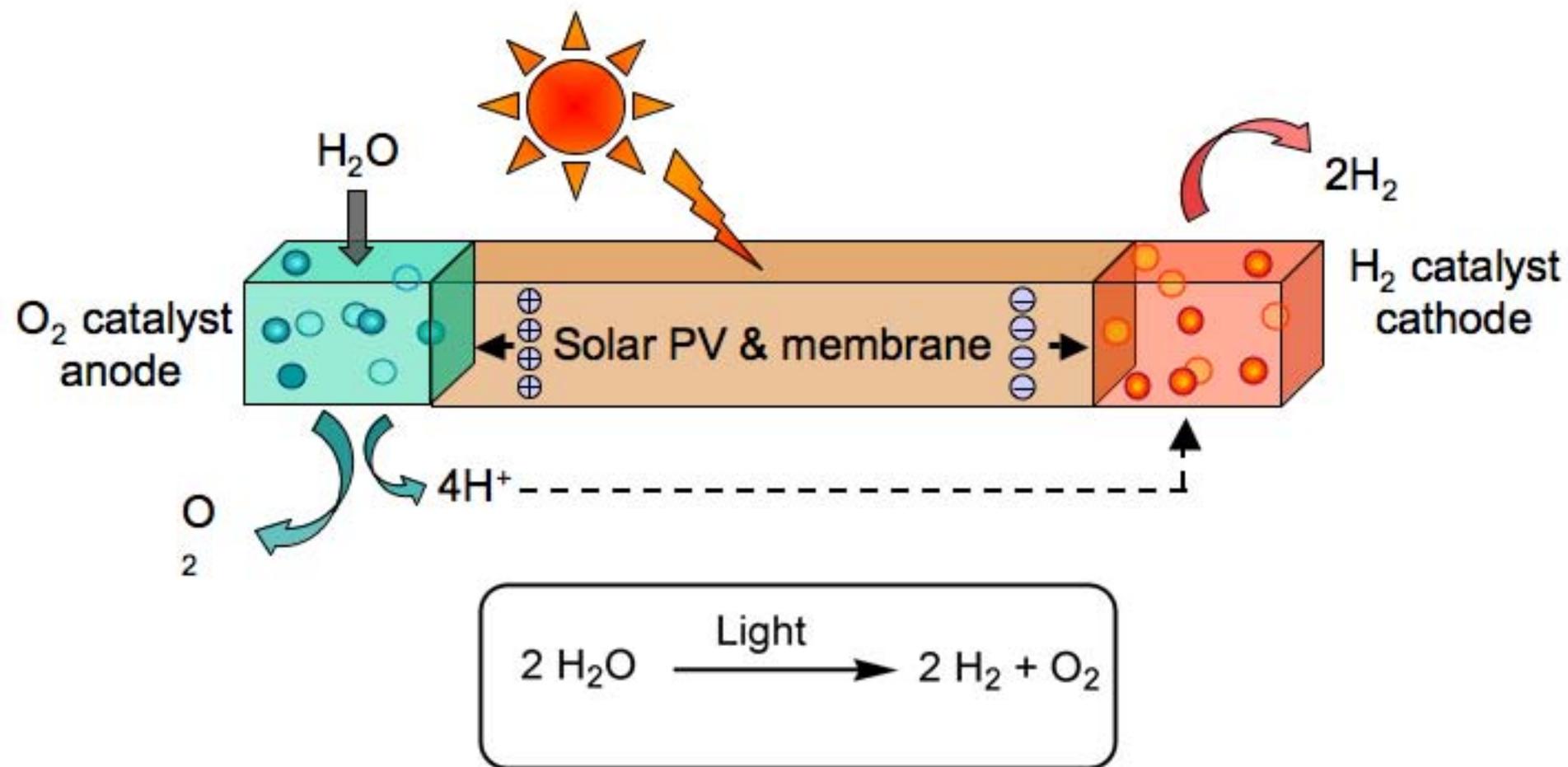


Fe_2O_3 Nanowires





System Concept





Conclusions



- Without **massive** quantities (10-20 TW by 2050) of clean energy, CO₂ levels will continue to rise
- The only sufficient supply-side cards we have are “clean” coal, nuclear fission (with a closed fuel cycle), and/or cheap solar fuel
- We need to pursue globally scalable systems that can efficiently and cost-effectively capture, convert, and store sunlight in the form of chemical fuels
 - He that can not store, will not have power after four
- Semiconductor/liquid junctions offer the *only* proven method for achieving this goal, but we have a great deal of fundamental science to learn to enable the underpinnings of a cost-effective, deployable technology
 - Nanorods, randomly ordered junctions to generate the needed potential
 - Catalysts to convert the incipient electrons into fuels by rearranging the chemical bonds of water (and CO₂) into O₂ and a reduced fuel